

ISL9538C

Buck-Boost Narrow VDC Battery Charger with SMBus Interface

The [ISL9538C](#) is a buck-boost Narrow Output Voltage DC (NVDC) charger. The ISL9538C provides NVDC charging, system bus regulation, and protection features for tablets, Ultrabooks, notebooks, power banks, and any USB-C interface platform. The advanced Renesas R3™ technology provides high light-load efficiency and fast transient response.

In Charging mode, the ISL9538C accepts input power from a wide range of DC power sources (such as conventional AC/DC charger adapters, USB PD ports, and travel adapters) and safely charges battery packs with up to 4-series cell Li-ion batteries.

As an NVDC topology charger, the ISL9538C also regulates the system output to a narrow DC range for stable system bus voltage. System power can be provided from the adapter, battery, or a combination of both. The ISL9538C can operate with only a battery, only an adapter, or with both connected. For Intel IMVP8 compliant systems, the ISL9538C includes PSYS (system power monitor) functionality, which provides an analog signal representing total platform power. The PSYS output connects to a wide range of Renesas IMVP8 core regulators to provide an IMVP8 compliant power domain function.

The ISL9538C supports buck, boost, or buck-boost operation to the input port from 2- to 4-cell batteries.

The ISL9538C provides SMBus/I²C serial communication that allows programming of many critical parameters to deliver a customized solution.

Features

- Buck-boost NVDC charger for 2-, 3-, or 4-cell Li-ion batteries
- Input voltage range: 3.9V to 23.4V (no dead zone)
- System output voltage: 2.4V to 18.304V
- Autonomous charging option (automatic completion of charging)
- Pass-Through mode in forward direction
- System power monitor PSYS output, IMVP compliant
- Up to 1MHz switching frequency
- Adapter current and battery current monitor (AMON/BMON)
- PROCHOT# open-drain output, IMVP compliant
- Allows trickle charging of depleted battery
- Ideal diode control in Turbo mode
- Two-level adapter current limit available
- 100% 2-FET Buck only mode option
- Battery Ship mode option
- SMBus and auto-increment I²C compatible
- 4x4 32 Ld TQFN package

Applications

- 2- to 4-cell tablets, Ultrabooks, notebooks, power banks, and any USB-C interface portable device requiring batteries

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1. Overview

1.1 Typical Application Diagrams

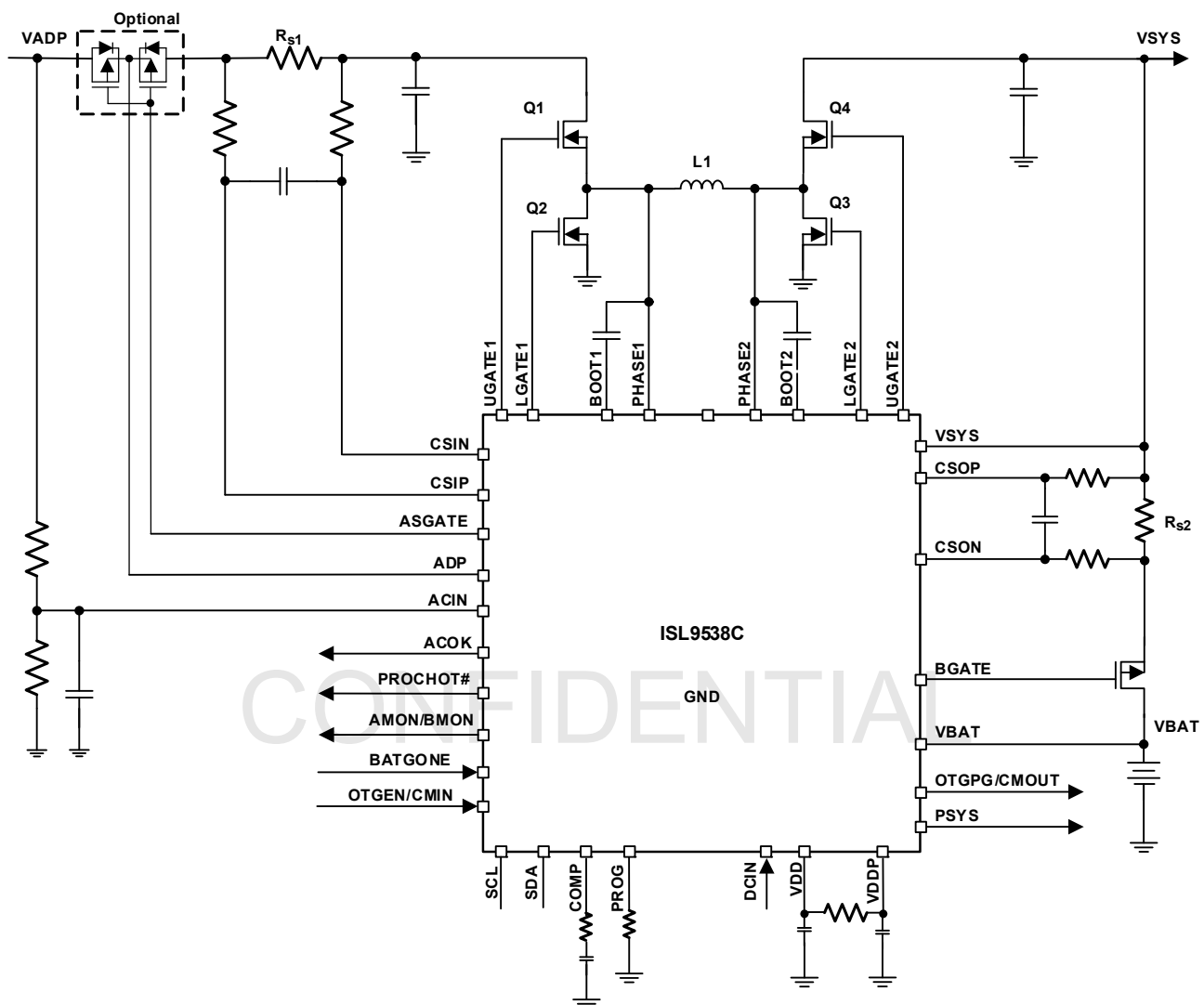


Figure 1. Typical Application Circuit

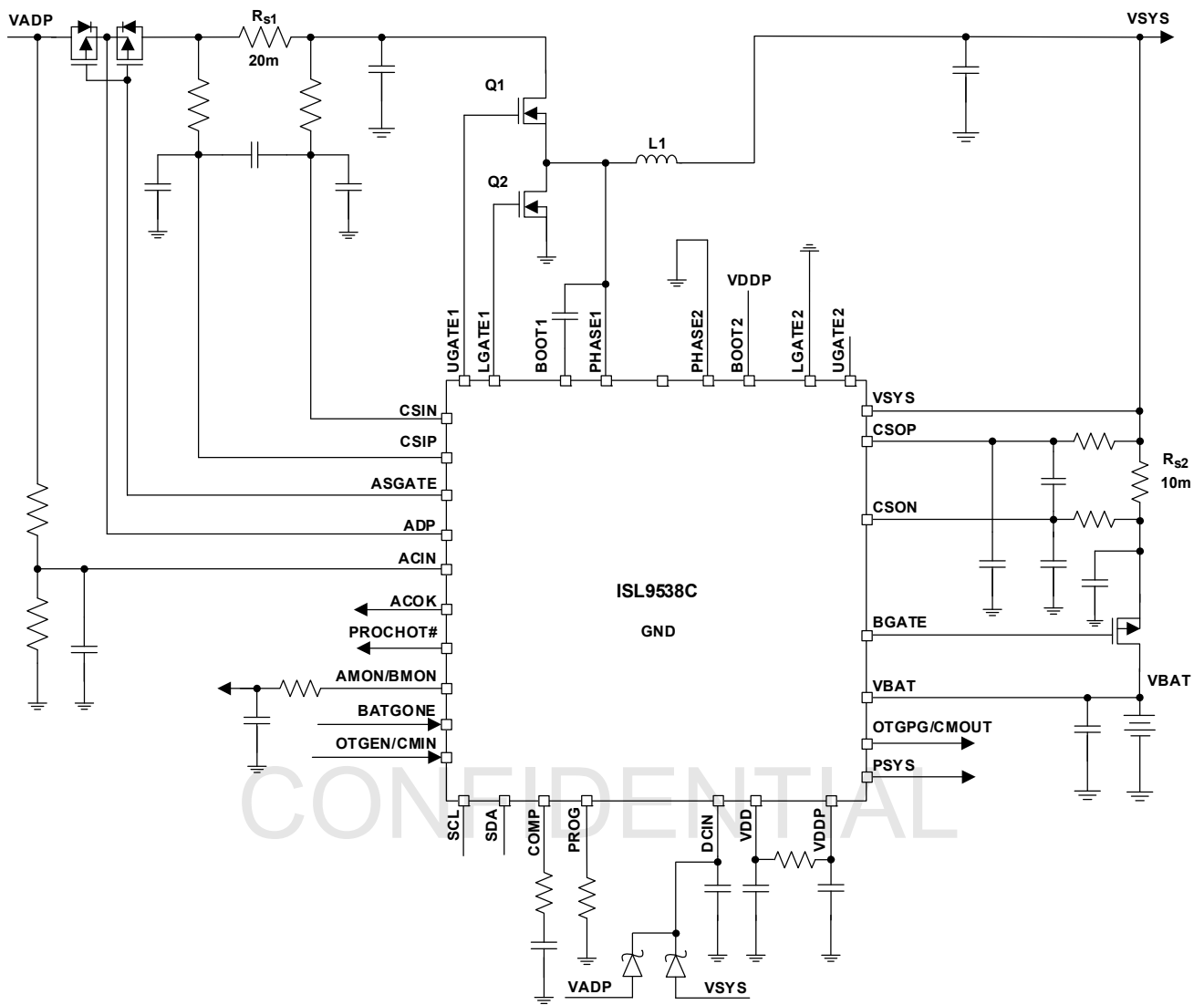


Figure 2. Simplified Application Diagram, Two FETs

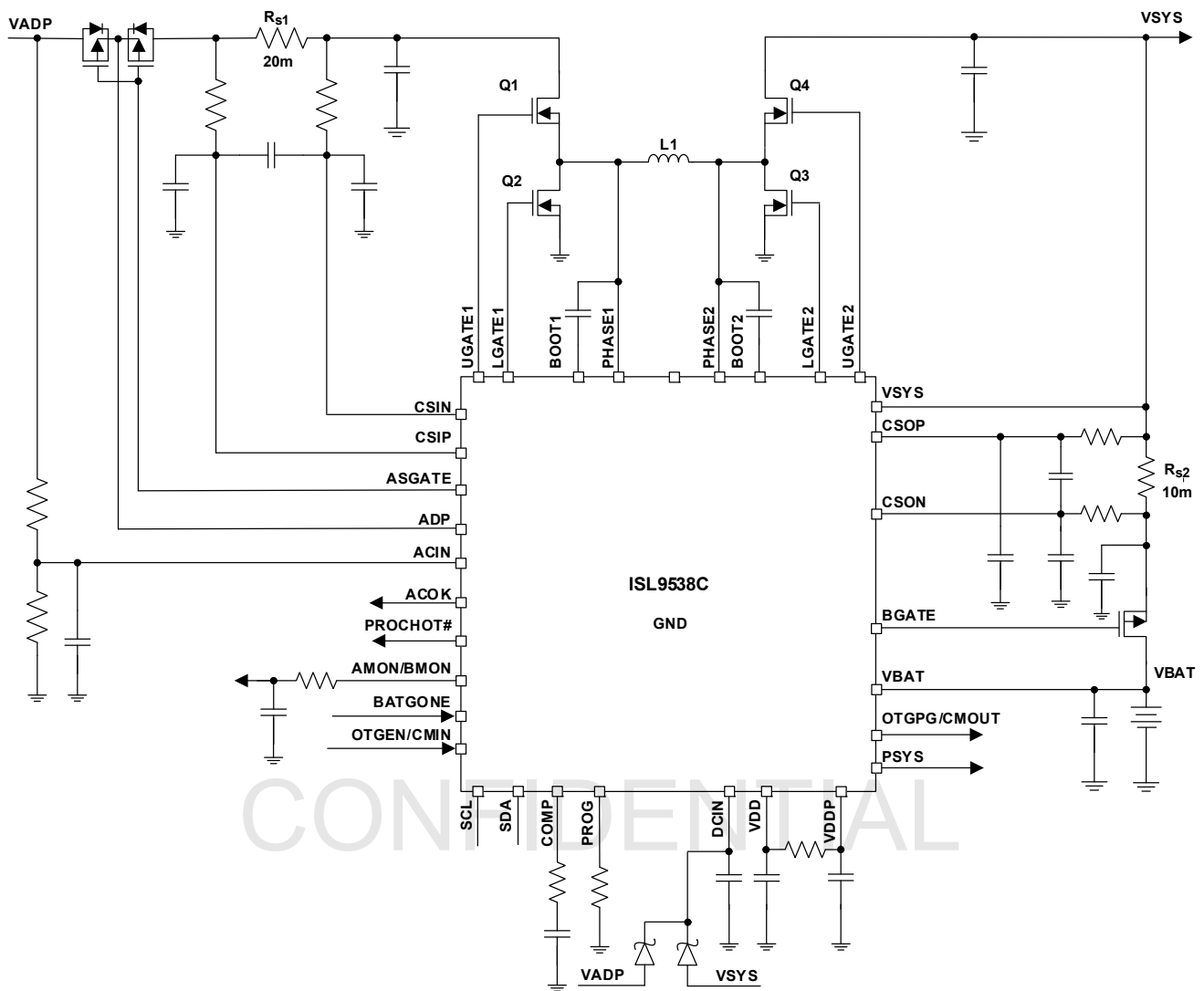


Figure 3. Simplified Application Diagram, Four FETs

1.2 Block Diagram

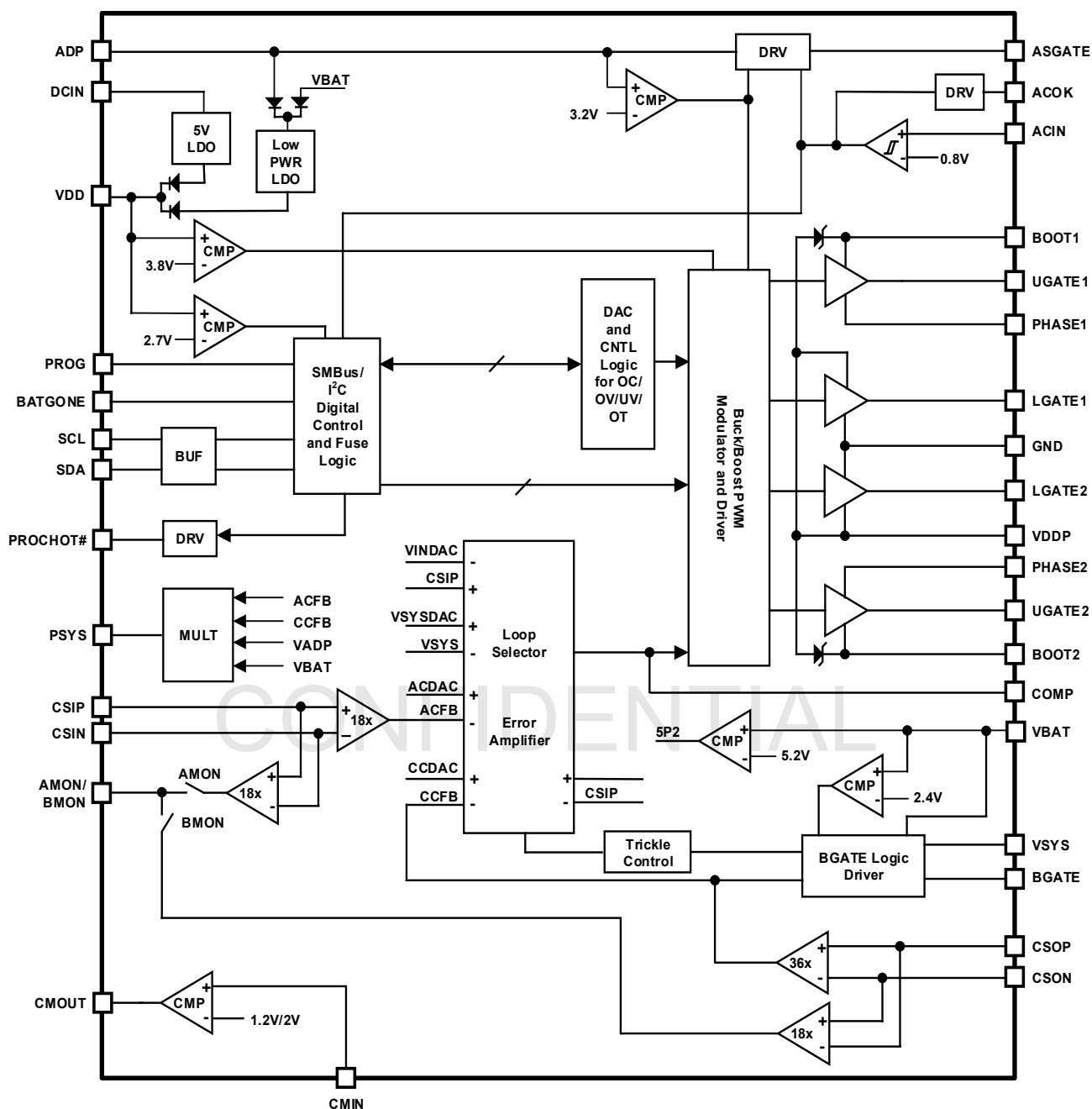


Figure 4. Block Diagram

1.3 Ordering Information

Part Number (Notes 2, 3)	Part Marking	Package Description (RoHS Compliant)	Pkg. Dwg. #	Carrier Type (Note 1)	Temp. Range
ISL9538CHRTZ	9538CH	32 Ld 4x4 TQFN	L32.4x4D	Tube	-10 to +100°C
ISL9538CHRTZ-T				Reel, 6k	
ISL9538CEVAL2Z	Evaluation Board				

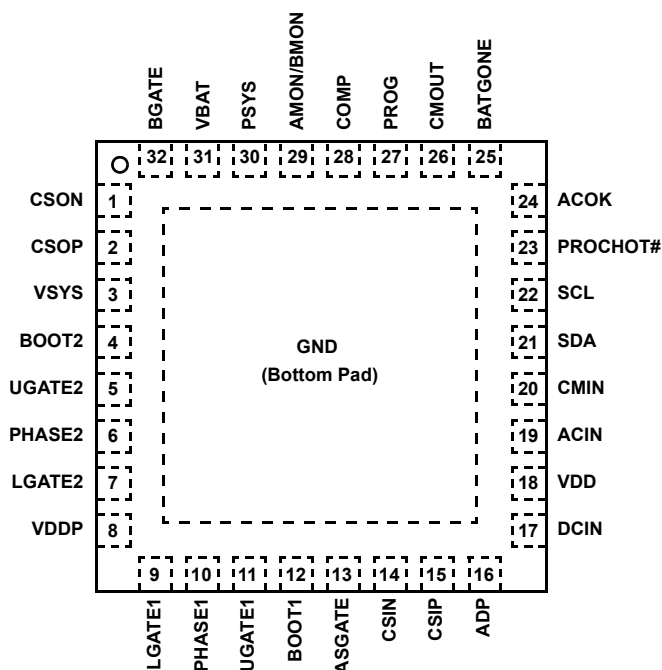
Notes:

- See [TB347](#) for details about reel specifications.
- These Pb-free plastic packaged products employ special Pb-free material sets, molding compounds/die attach materials, and 100% matte tin plate plus anneal (e3 termination finish, which is RoHS compliant and compatible with both SnPb and Pb-free soldering operations). Pb-free products are MSL classified at Pb-free peak reflow temperatures that meet or exceed the Pb-free requirements of IPC/JEDEC J STD-020.
- For the Moisture Sensitivity Level (MSL), see the Product Options on the [ISL9538C](#) product page (click the packaging icon). For more information about MSL, see [TB363](#).

Table 1. Key Differences Between Family of Parts

Part Number	OTG	OTG Current Limit LSB	Force Buck Mode	Pass-Through Mode	Drop-In Pin-to-Pin
ISL9538C	N/A	N/A	Yes	Yes	Yes
ISL9538B	N/A	N/A	Yes	Yes	Yes
ISL9538	N/A	N/A	N/A	N/A	Yes
ISL9238C	5V - 20V	32mA	Yes	Yes	Yes
ISL9238	5V - 20V	128mA	N/A	N/A	Yes
ISL9238A	5V - 20V	128mA	N/A	N/A	Yes
ISL9237	4.864V - 5.376V	128mA	N/A	N/A	Yes
ISL95538B	5V - 20V	128mA	N/A	N/A	Yes

1.4 Pin Configuration

 32 LD 4x4 TQFN
Top View


1.5 Pin Descriptions

Pin Number	Pin Name	Description
Bottom Pad	GND	Signal common to the IC. Unless otherwise stated, signals are referenced to the GND pin. GND should also be used as the thermal pad for heat dissipation.
1	CSON	Battery current sense “–” input. Connect to the battery current resistor negative input. Place a ceramic capacitor between CSOP to CSON to provide Differential mode filtering.
2	CSOP	Battery current sense “+” input. Connect to the battery current resistor positive input. Place a ceramic capacitor between CSOP to CSON to provide Differential mode filtering.
3	VSYS	Provides feedback voltage for MaxSystemVoltage regulation.
4	BOOT2	High-side MOSFET Q4 gate driver supply. Connect an MLCC capacitor across the BOOT2 and PHASE2 pins. The boot capacitor is charged through an internal boot diode connected from the VDDP to BOOT2 pins when the PHASE2 pin drops below VDDP minus the voltage drop across the internal boot diode. Connect a 0.47μF (25V) bootstrap capacitor, which must have an effective capacitance higher than 0.25μF at 5V and x50 effective high-side MOSFET gate capacitance.
5	UGATE2	High-side MOSFET Q4 gate drive.
6	PHASE2	Current return path for the high-side MOSFET Q4 gate drive. Connect this pin to the node consisting of the high-side MOSFET Q4 source, the low-side MOSFET Q3 drain, and one terminal of the inductor.
7	LGATE2	Low-side MOSFET Q3 gate drive.
8	VDDP	Power supply for the gate drivers. Connect to the VDD pin through a 4.7Ω resistor and connect a 2.2μF (10V) MLCC capacitor to GND. The capacitor must have an effective capacitance higher than 0.4μF at 5V and x1.6 effective capacitance at the BOOT pin at 5V.
9	LGATE1	Low-side MOSFET Q2 gate drive.
10	PHASE1	Current return path for the high-side MOSFET Q1 gate drive. Connect this pin to the node consisting of the high-side MOSFET Q1 source, the low-side MOSFET Q2 drain, and the input terminal of the inductor.
11	UGATE1	High-side MOSFET Q1 gate drive.
12	BOOT1	High-side MOSFET Q1 gate driver supply. Connect an MLCC capacitor across the BOOT1 and PHASE1 pins. The boot capacitor is charged through an internal boot diode connected from the VDDP to BOOT1 pins when the PHASE1 pin drops below VDDP minus the voltage drop across the internal boot diode. Connect a 0.47μF (25V) bootstrap capacitor, which must have an effective capacitance higher than 0.25μF at 5V and x50 effective high side MOSFET gate capacitance.
13	ASGATE	Gate drive output to the P-channel adapter FET. The use of ASGATE FETs is optional. If they are not used, leave the ASGATE pin floating. When ASGATE turns on, it is clamped 10V below the ADP pin's voltage.
14	CSIN	Adapter current sense “–” input.
15	CSIP	Adapter current sense “+” input. The modulator also uses the CSIP pin for sensing input voltage.
16	ADP	Adapter input used to sense adapter voltage. AGATE is turned on when the adapter voltage is higher than 3.2V. The ADP pin is also one of the two internal low power LDO inputs.
17	DCIN	Internal LDO input that provides power to the IC. Connect a diode OR from the adapter and system outputs. Bypass DCIN with an MLCC capacitor. Connect a 10Ω DCIN resistor between the DCIN pin and the VADP/VSYS diodes, and connect a 4.7μF DCIN capacitor to GND. The capacitor must have an effective capacitance higher than 0.4μF at 20V.
18	VDD	Internal LDO output that provides the bias power for the internal analog and digital circuit. Connect a 2.2μF (10V) MLCC capacitor to GND. The capacitor must have an effective capacitance higher than 0.4μF at 5V and x1.6 effective capacitance at the BOOT pin at 5V. If VDD is pulled below 2V for more than 1ms, the ISL9538C resets all the SMBus register values to their defaults.
19	ACIN	Adapter voltage sense. Use a resistor divider externally to detect adapter voltage. The adapter voltage is valid if the ACIN pin voltage is greater than 0.8V.
20	CMIN	Stand-alone comparator input pin.
21	SDA	SMBus data I/O. Connect to the data line from the host controller or smart battery. Connect a 10k pull-up resistor according to the SMBus specification.
22	SCL	SMBus clock I/O. Connect to the clock line from the host controller or smart battery. Connect a 10k pull-up resistor according to the SMBus specification.
23	PROCHOT#	Open-drain output. Pulled low when ACHOT, DCHOT, or Low_VSYS are detected. IMVP-8 compliant. Send an SMBus command to pull low with BATGONE, ACOK, and the general purpose comparator (see Table 15).

Pin Number	Pin Name	Description
24	ACOK	Adapter presence indicator output to indicate the adapter is ready.
25	BATGONE	Input pin to the IC. Logic high on this pin indicates the battery has been removed. Logic low on this pin indicates the battery is present. BATGONE pin logic high forces the BGATE FET to turn off in any circumstances.
26	CMOUT	Open-drain output. Stand-alone comparator output.
27	PROG	A resistor from the PROG pin to GND sets the following configurations: • Default number of the battery cells in series: 2-, 3-, or 4-cell • Default switching frequency: 733kHz or 1MHz • Default adapter current limit value: 0.476A or 1.5A • Autonomous Charging mode: Enabled or disabled See Table 25 for programming options.
28	COMP	Error amplifier output. Connect a compensation network externally from COMP to GND.
29	AMON/ BMON	Adapter current, battery charging current, or battery discharging current monitor output. • $V_{AMON} = 18x (V_{CSIP} - V_{CSIN})$ for adapter current monitor • $V_{BMON_DISCHARGING} = 18x (V_{CSON} - V_{CSOP})$ for battery discharging current monitor • $V_{BMON_CHARGING} = 36x (V_{CSOP} - V_{CSON})$ for battery charging current monitor
30	PSYS	Current source output that indicates the whole platform power consumption. PSYS gain = 1.467 μ A/W (default) or 0.734 μ A/W
31	VBAT	Battery voltage sensor. Used for trickle charging detection and Ideal Diode mode control. Connect a >1 μ F ceramic capacitor from VBAT to GND. The VBAT pin is also one of the two internal low power LDO inputs.
32	BGATE	Gate drive output to the P-channel FET connecting the system and the battery. This pin can go high to disconnect the battery, or low to connect the battery or operate in Linear mode to regulate the trickle charge current during trickle charge. When BGATE turns on, it is clamped 10V below the VSYS pin voltage.

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2. Specifications

2.1 Absolute Maximum Ratings

Parameter	Minimum	Maximum	Units
CSIP, CSIN, DCIN, ADP, ASGATE	-0.3	+28	V
PHASE1	GND - 0.3	+28	V
PHASE1	GND - 2 (<20ns)	+28	V
BOOT1, UGATE1	GND - 0.3	+33	V
PHASE2	GND - 0.3	+24	V
PHASE2	GND - 2 (<20ns)	+24	V
BOOT2, UGATE2	GND - 0.3	+29	V
LGATE1, LGATE2	GND - 0.3	+6.5	V
LGATE1, LGATE2	GND - 2 (<20ns)	+6.5	V
VBAT, VSYS, CSOP, CSON, BGATE	-0.3	+24	V
VDD, VDDP	-0.3	+6.5	V
COMP	-0.3	+6.5	V
AMON/BMON, PSYS	-0.3	+6.5	V
CMIN, BATGONE	-0.3	+6.5	V
ACIN, PROCHOT#	-0.3	+6.5	V
SCL, SDA	-0.3	+6.5	V
BOOT1 - PHASE1, BOOT2 - PHASE2	-0.3	+6.5	V
CSIP - CSIN, CSOP - CSON	-0.3	+0.3	V
PROCHOT#, ACOK		2	mA
ESD Rating	Value		Unit
Human Body Model (Tested per JS-001-2017)	2.5		kV
Charged Device Model (Tested per JS-002-2014)	1		kV
Latch-Up (Tested per JESD78E; Class 2, Level A)	100		mA

CAUTION: Do not operate at or near the maximum ratings listed for extended periods of time. Exposure to such conditions can adversely impact product reliability and result in failures not covered by warranty.

2.2 Thermal Information

Thermal Resistance (Typical)	θ_{JA} (°C/W)	θ_{JC} (°C/W)
32 Ld TQFN Package (Notes 4, 5)	37	2

Notes:

- θ_{JA} is measured in free air with the component mounted on a high-effective thermal conductivity test board with direct attach features. See [TB379](#).
- For θ_{JC} , the case temperature location is the center of the exposed metal pad on the package underside.

Parameter	Minimum	Maximum	Unit
Junction Temperature Range (T_J)	-10	+125	
Storage Temperature Range (T_S)	-65	+175	°C
Pb-Free Reflow Profile	See TB493		

2.3 Recommended Operating Conditions

Parameter	Minimum	Maximum	Unit
Ambient Temperature, HRTZ	-10	+100	°C
Junction Temperature	-10	+125	°C
Adapter Voltage	4	23	V

2.4 Electrical Specifications

Operating conditions: ADP = CSIP = CSIN = 5V and 20V, $V_{SYS} = V_{BAT} = CSOP = CSON = 8V$, unless otherwise noted. **Boldface limits apply across the junction temperature range, -10°C to +125°C unless otherwise specified.**

Parameter	Symbol	Test Conditions	Min (Note 6)	Typ	Max (Note 6)	Unit
UVLO/ACOK						
VADP UVLO Rising	VADP_UVLO_r		3.1	3.3	3.5	V
VADP UVLO Hysteresis	VADP_UVLO_h			600		mV
V _{BAT} UVLO Rising	VBAT_UVLO_r		2.30	2.45	2.65	V
V _{BAT} UVLO Hysteresis	VBAT_UVLO_h			400		mV
V _{BAT} 5P2V Rising	VBAT_5P2_r		5.05	5.20	5.7	V
V _{BAT} 5P2V Hysteresis	VBAT_5P2_h			490		mV
VDD 2P7 POR Falling, SMBus and BGATE/BMON Active Threshold	VDD_2P7_f		2.50	2.70	2.9	V
VDD 2P7 POR Hysteresis	VDD_2P7_h			150		mV
VDD 3P8 POR Rising, Modulator and Gate Driver Active	VDD_3P8_r		3.6	3.8	3.9	V
VDD 3P8 POR Hysteresis	VDD_3P8_h			150		mV
ACIN Rising	ACIN_r		0.775	0.800	0.825	V
ACIN Hysteresis	ACIN_h			50		mV
Linear Regulator						
VDD Output Voltage	VDD	6V < V _{DCIN} < 23V, no load	4.5	5.0	5.5	V
VDD Dropout Voltage	VDD_dp	30mA, V _{DCIN} = 4V		85		mV
VDD Overcurrent Threshold	VDD_OC		80	120	155	mA
Battery Current	I _{BAT1}	Battery only, BGATE on, PSYS OFF, BMON OFF, V _{BAT} = 16.8V, DCIN current comes from battery, I _{BAT} = I _{VBAT} + I _{CSOP} + I _{CSON} + I _{DCIN} + I _{VSYS}		24	50	μA
	I _{BAT2}	Battery only, BGATE on, PSYS OFF, BMON ON, V _{BAT} = 16.8V, DCIN current comes from battery, I _{BAT} = I _{VBAT} + I _{CSOP} + I _{CSON} + I _{DCIN} + I _{VSYS}		74		μA
	I _{BAT3}	Battery only, BGATE on, PSYS ON, BMON OFF, V _{BAT} = 16.8V, DCIN current comes from battery, I _{BAT} = I _{VBAT} + I _{CSOP} + I _{CSON} + I _{DCIN} + I _{VSYS}		905	1200	μA
Adapter Current Regulation, R_{S1} = 20mΩ						
Adapter Current Accuracy		CSIP - CSIN = 80mV		4		A
			-2		2	%
		CSIP - CSIN = 40mV		2		A
			-2.5		2.5	%
		CSIP - CSIN = 10mV		0.5		A
			-10		10	%

Operating conditions: ADP = CSIP = CSIN = 5V and 20V, $V_{SYS} = V_{BAT} = CSOP = CSON = 8V$, unless otherwise noted. **Boldface limits apply across the junction temperature range, -10°C to +125°C unless otherwise specified. (Continued)**

Parameter	Symbol	Test Conditions	Min (Note 6)	Typ	Max (Note 6)	Unit
Adapter Current PROCHOT# Threshold R _{S1} = 20mΩ	I _{ADP_HOT_TH10}	ACProchot = 0x1580H (5504mA)		5504		mA
			-1.5		1.5	%
		ACProchot = 0x0A80H (2688mA)		2688		mA
			-3.0		3.0	%
		ACProchot = 0x0400H (1024mA)		1024		mA
			-6.0		6.0	%
System Voltage Regulation						
Maximum System Voltage Accuracy		MaxSystemVoltage for 2-cell (8.4V)	-0.6		0.6	%
		MaxSystemVoltage for 3-cell and 4-cell (12.6V and 16.8V)	-0.5		0.5	%
Minimum System Voltage Accuracy		VDAC = 5V to 14V	-3		3	%
Input Voltage Regulation Accuracy		Input Voltage Register = 4.096V	3.98		4.22	V
Charge Current Regulation, R _{S2} = 10mΩ (Limits apply across temperature range of 0°C to +85°C)						
Charge Current Accuracy		CSOP - CSON = 60mV		6		A
			-2.5		2.5	%
		CSOP - CSON = 20mV		2		A
			-4		4	%
		CSOP - CSON = 10mV		1		A
			-6		6	%
		CSOP - CSON = 5mV		0.5		A
	-12		12	%		
BGATE Clamp						
VSYS - VBGATE ON		Charging enabled	6.80	8.30	9.16	V
VSYS - VBGATE OFF		Charging disabled		0		V
ASGATE Clamp						
VADP - VASGATE ON				12		V
VSYS - VBGATE OFF				0		V
Trickle Charging Current Regulation, R _{S2} = 10mΩ (Limits apply across temperature range of 0°C to +85°C)						
Trickle Charge Current Accuracy		Trickle, 512mA	410	512	614	mA
		Trickle, 256mA	205	256	334	mA
		Trickle, 128mA	77	128	192	mA
		Trickle, 64mA	16	64	128	mA
Fast Charge to Trickle Charge Threshold		V _{SY} S - V _{BGATE}	4.23	5.18	5.97	V
Trickle Charge to Fast Charge Threshold Hysteresis		V _{SY} S - V _{BGATE}	50	130	260	mV
Fast Charge to Trickle Charge BGATE Threshold		V _{SY} S > 7V, V _{FB} >> V _{REF}		1.15		V
Trickle Charge to Fast Charge BGATE Threshold Hysteresis		V _{SY} S > 7V, V _{FB} >> V _{REF}		50		mV
Ideal Diode Mode						
Entering Ideal Diode Mode VSYS Voltage Threshold		BGATE off, VSYS falling V _{VBAT} - CSON	100	150	200	mV
Exiting Ideal Diode Mode Battery Discharging Current Threshold		R _{S2} = 10mΩ	110	200	290	mA

Operating conditions: ADP = CSIP = CSIN = 5V and 20V, $V_{SYS} = V_{BAT} = CSOP = CSON = 8V$, unless otherwise noted. **Boldface limits apply across the junction temperature range, -10°C to +125°C unless otherwise specified. (Continued)**

Parameter	Symbol	Test Conditions	Min (Note 6)	Typ	Max (Note 6)	Unit
Exiting Ideal Diode Mode Battery Charging Current Threshold		$R_{S2} = 10m\Omega$	50	130	200	mA
BGATE Source		$V_{SYS} - BGATE = 2V$, charging disabled	4	6	10	mA
BGATE Sink		$BGATE - GND = 2V$, charging enabled	20	30	40	μA
BGATE Sink		$BGATE - GND = 2V$, in Ideal Diode mode		6		mA
AMON/BMON						
Input Current Sense Amplifier, $R_{S1} = 20m\Omega$						
CSIP/CSIN Input Voltage Range			4		23	V
AMON Gain				17.97		V/V
AMON Accuracy $V_{AMON} = 17.97 \times (CSIP - CSIN)$		$V_{CSIP} - V_{CSIN} = 100mV$ (5A), CSIP = 5V - 20V	-2		2	%
		$V_{CSIP} - V_{CSIN} = 20mV$ (1A), CSIP = 5V - 20V	-5		5	%
		$V_{CSIP} - V_{CSIN} = 10mV$ (0.5A), CSIP = 5V - 20V	-10		10	%
		$V_{CSIP} - V_{CSIN} = 2mV$ (0.1A), CSIP = 5V - 20V	-40		40	%
AMON Minimum Output Voltage		$V_{CSIP} - V_{CSIN} = 0V$			30	mV
Discharge Current Sense Amplifier, $R_{S2} = 10m\Omega$						
BMON Gain (Battery Discharging)				17.97		V/V
BMON Accuracy $V_{BMON} = 17.97 \times (V_{CSON} - V_{CSOP})$		$V_{CSON} - V_{CSOP} = 100mV$ (10A), $V_{CSON} = 8V$	-2.5		2.5	%
		$V_{CSON} - V_{CSOP} = 20mV$ (2A), $V_{CSON} = 8V$	-7.0	-1.5	4.0	%
		$V_{CSON} - V_{CSOP} = 10mV$ (1A), $V_{CSON} = 8V$	-10.5	-2.5	5.5	%
		$V_{CSON} - V_{CSOP} = 6mV$ (0.6A), $V_{CSON} = 8V$	-17	-4	12	%
Charge Current Sense Amplifier, $R_{S2} = 10m\Omega$ (Limits apply across temperature range of 0°C to +85°C)						
BMON Gain (Battery Charging)		Limits apply across temperature range of 0°C to +85°C		35.78		V/V
BMON Accuracy $V_{BMON} = 35.78 \times (V_{CSON} - V_{CSOP})$		$V_{CSOP} - V_{CSON} = 60mV$ (6A), $V_{CSON} = 8V$	-3		3	%
		$V_{CSOP} - V_{CSON} = 40mV$ (4A), $V_{CSON} = 8V$	-4		4	%
		$V_{CSOP} - V_{CSON} = 10mV$ (1A), $V_{CSON} = 8V$	-10		10	%
		$V_{CSOP} - V_{CSON} = 5mV$ (0.5A), $V_{CSON} = 8V$	-25		25	%
BMON Minimum Output Voltage		$V_{CSOP} - V_{CSON} = 0V$			30	mV
Discharging Current PROCHOT# Threshold, $R_{S2} = 10m\Omega$	$I_{DIS_HOT_TH}$	DCProchot = 2.048A	1.77	2.08	2.39	A
Discharging Current PROCHOT# Threshold, Battery Only, $R_{S2} = 10m\Omega$	$I_{DIS_HOT_TH}$	DCProchot = 12A	10.8	13.5	17	A
		DCProchot = 6A	5.2	6.5	8	A
AMON/BMON Source Resistance		(Note 7)			5	Ω
AMON/BMON Sink Resistance		(Note 7)			5	Ω

Operating conditions: ADP = CSIP = CSIN = 5V and 20V, $V_{SYS} = V_{BAT} = CSOP = CSON = 8V$, unless otherwise noted. **Boldface limits apply across the junction temperature range, -10°C to +125°C unless otherwise specified. (Continued)**

Parameter	Symbol	Test Conditions	Min (Note 6)	Typ	Max (Note 6)	Unit
BATGONE						
High-Level Input Voltage			0.9			V
Low-Level Input Voltage					0.4	V
Pull-Down Current		BATGONE - 5V		5		μA
PROCHOT#						
PROCHOT# Debounce Time		PROCHOT# Debounce register Bit<1:0> = 11	0.85	1	1.15	ms
		PROCHOT# Debounce register Bit<1:0> = 10	425	500	575	μs
PROCHOT# Duration Time		PROCHOT# Duration register Bit<2:0> = 011	8.5	10	11.5	ms
		PROCHOT# Duration register Bit<2:0> = 001	17	20	23	ms
Low VSYS PROCHOT# Trip Threshold	V _{LOW_VSYS_HOT}	Control1 register Bit<1:0> = 00	5.8	6.0	6.2	V
		Control1 register Bit<1:0> = 01	6.1	6.3	6.5	V
		Control1 register Bit<1:0> = 10	6.4	6.6	6.8	V
		Control1 register Bit<1:0> = 11	6.7	6.9	7.1	V
PSYS						
PSYS Output Current (Note 7) R _{s1} = 20mΩ R _{s2} = 10mΩ	I _{PSYS} Control3 Bit<9> = 0 I _{PSYS} = 1.467 x Power + 1.43μA	V _{CSIP} = 20V, V _{CSIP-CSIN} = 40mV, V _{BAT} = 12V, V _{CSOP-CSON} = -10mV	-5		5	%
	I _{PSYS} Control3 Bit<9> = 1 I _{PSYS} = 0.734 x Power	V _{CSIP} = 19V, V _{CSIP-CSIN} = 80mV, V _{BAT} = 12V, V _{CSOP-CSON} = -20mV	-5		5	%
Maximum PSYS Output Voltage	V _{PSYS_MAX}		4			V
General Purpose Comparator						
General Purpose Comparator Rising Threshold		Reference = 1.2V	1.11	1.2	1.29	V
		Reference = 2V	1.95	2	2.05	V
General Purpose Comparator Hysteresis		Reference = 1.2V		45		mV
		Reference = 2V		45		mV
Protection						
VSYS Overvoltage Rising Threshold		MaxSystemVoltage register value = 8.4V	8.92	9.15	9.38	V
VSYS Overvoltage Hysteresis			250	400	550	mV
VSYS UV Falling Threshold		Control6 register Bit<2:0> = 001		3		V
		Control6 register Bit<2:0> = 010		3.9		V
		Control6 register Bit<2:0> = 011		4.8		V
		Control6 register Bit<2:0> = 100		5.7		V
		Control6 register Bit<2:0> = 101		6.6		V
		Control6 register Bit<2:0> = 110		7.5		V
		Control6 register Bit<2:0> = 111		8.4		V
VSYS OK Threshold			0.45	0.6	0.75	V
VSYS OK Source Current				10		mA
Over-Temperature Threshold (Note 7)			140	150	160	°C

Operating conditions: ADP = CSIP = CSIN = 5V and 20V, $V_{SYS} = V_{BAT} = CSOP = CSON = 8V$, unless otherwise noted. **Boldface limits apply across the junction temperature range, -10°C to +125°C unless otherwise specified. (Continued)**

Parameter	Symbol	Test Conditions	Min (Note 6)	Typ	Max (Note 6)	Unit
Adapter Overvoltage Rising Threshold			22.5	23.4	24	V
Adapter Overvoltage Hysteresis			150	350	500	mV
Oscillator						
Oscillator Frequency, Digital Core Only			0.85	1	1.15	MHz
Digital Debounce Time Accuracy (Note 7)			-15		15	%
Miscellaneous						
Switching Frequency Accuracy		COMP > 1.7V and not in period stretching	-15		15	%
Battery Learn Mode Auto-Exit Threshold		MinSystemVoltage = 5.376V Control1 register Bit<13> = 1	5.05	5.35	5.7	V
Battery Learn Mode Auto-Exit Hysteresis (Note 7)			180	330	480	mV
ADP Discharge Current		ADP = 5V to 20V		15		mA
VSYS Discharge Current		VSYS = 5V to 18V		10		mA
SMBus						
SDA/SCL Input Low Voltage					0.6	V
SDA/SCL Input High Voltage			1.3			V
SDA/SCL Input Bias Current					1	μA
SDA, Output Sink Current		SDA = 0.4V	4			mA
SMBus Frequency	f_{SMB}		10		400	kHz
Gate Driver (Note 7)						
UGATE1 Pull-Up Resistance	UG1 _{RPU}	100mA source current		800	1200	mΩ
UGATE1 Source Current	UG1 _{SRC}	UGATE1 - PHASE1 = 2.5V	1.3	2		A
UGATE1 Pull-Down Resistance	UG1 _{RPD}	100mA sink current		350	475	mΩ
UGATE1 Sink Current	UG1 _{SNK}	UGATE1 - PHASE1 = 2.5V	1.9	2.8		A
LGATE1 Pull-Up Resistance	LG1 _{RPU}	100mA source current		800	1200	mΩ
LGATE1 Source Current	LG1 _{SRC}	LGATE1 - GND = 2.5V	1.3	2		A
LGATE1 Pull-Down Resistance	LG1 _{RPD}	100mA sink current		300	450	mΩ
LGATE1 Sink Current	LG1 _{SNK}	LGATE1 - GND = 2.5V	2.3	3.5		A
LGATE2 Pull-Up Resistance	LG2 _{RPU}	100mA source current		800	1200	mΩ
LGATE2 Source Current	LG2 _{SRC}	LGATE2 - GND = 2.5V	1.3	2		A
LGATE2 Pull-Down Resistance	LG2 _{RPD}	100mA sink current		300	450	mΩ
LGATE2 Sink Current	LG2 _{SNK}	LGATE2 - GND = 2.5V	2.3	3.5		A
UGATE2 Pull-Up Resistance	UG2 _{RPU}	100mA source current		800	1200	mΩ
UGATE2 Source Current	UG2 _{SRC}	UGATE2 - PHASE2 = 2.5V	1.3	2		A
UGATE2 Pull-Down Resistance	UG2 _{RPD}	100mA sink current		300	450	mΩ
UGATE2 Sink Current	UG2 _{SNK}	UGATE2 - PHASE2 = 2.5V	2.3	3.5		A
UGATE1 to LGATE1 Dead Time	$t_{UG1LG1DEAD}$		10	20	40	ns
LGATE1 to UGATE1 Dead Time	$t_{LG1UG1DEAD}$		10	20	40	ns
LGATE2 to UGATE2 Dead Time	$t_{LG2UG2DEAD}$		10	20	40	ns
UGATE2 to LGATE2 Dead Time	$t_{UG2LG2DEAD}$		10	20	40	ns

Operating conditions: ADP = CSIP = CSIN = 5V and 20V, $V_{SYS} = V_{BAT} = CSOP = CSON = 8V$, unless otherwise noted. **Boldface limits apply across the junction temperature range, -10°C to +125°C unless otherwise specified. (Continued)**

Parameter	Symbol	Test Conditions	Min (Note 6)	Typ	Max (Note 6)	Unit
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Note:

6. Parameters with MIN and/or MAX limits are 100% tested at +25°C, unless otherwise specified. Temperature limits established by characterization and are not production tested.

2.5 SMBus Timing Specifications

Parameters	Symbol	Test Conditions	Min (Note 7)	Typ	Max (Note 7)	Unit
SMBus Frequency	f_{SMB}		10		400	kHz
Bus Free Time	t_{BUF}		4.7			μs
Start Condition Hold Time from SCL	$t_{HD:STA}$		4			μs
Start Condition Set-Up Time from SCL	$t_{SU:STA}$		4.7			μs
Stop Condition Set-Up Time from SCL	$t_{SU:STO}$		4			μs
SDA Hold Time from SCL	$t_{HD:DAT}$		300			ns
SDA Set-Up Time from SCL	$t_{SU:DAT}$		250			ns
SCL Low Period	t_{LOW}		4.7			μs
SCL High Period	t_{HIGH}		4			μs
SMBus Inactivity Timeout		Maximum charging period without a SMBus Write to MaxSystemVoltage or ChargeCurrent register		175		s

Note:

7. Limits established by characterization and are not production tested.

2.6 Gate Driver Timing Diagram

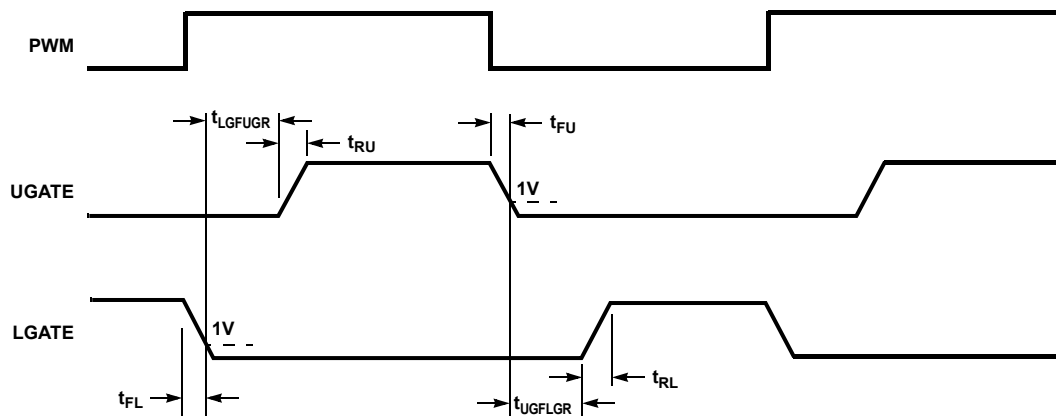


Figure 5. Gate Driver Timing Diagram

3. Typical Performance

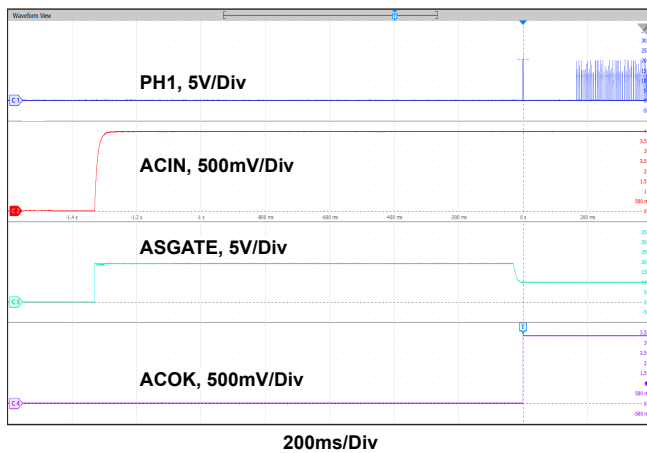


Figure 6. Adapter Insertion, $V_{ADP} = 20V$, $V_{BAT} = 11V$, ChargeCurrent = 0A

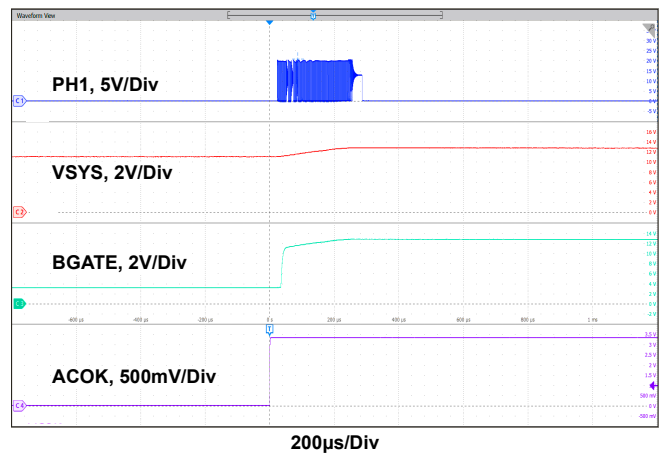


Figure 7. Adapter Insertion, $V_{ADP} = 20V$, $V_{BAT} = 11V$, ChargeCurrent = 0A (Figure 6 Zoomed In)

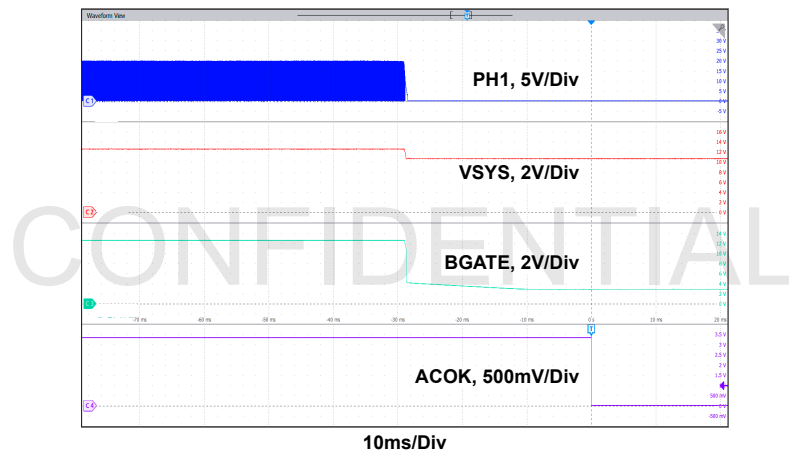


Figure 8. Adapter Removal, $V_{ADP} = 20V$, $V_{BAT} = 11V$, ChargeCurrent = 0A

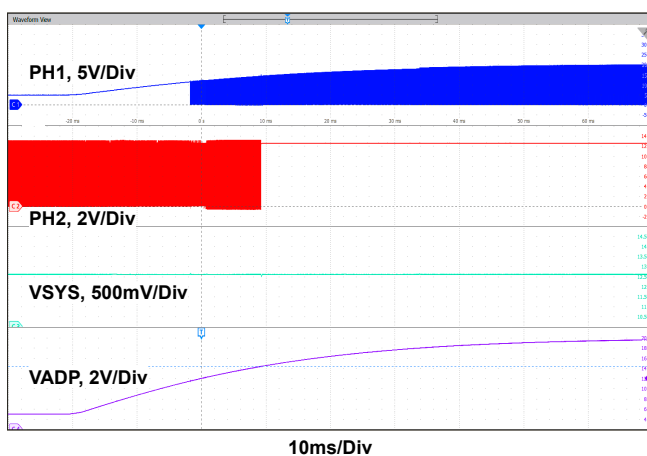


Figure 9. Adapter Voltage Ramps Up, Boost → Buck-Boost → Buck Operation Mode Transition

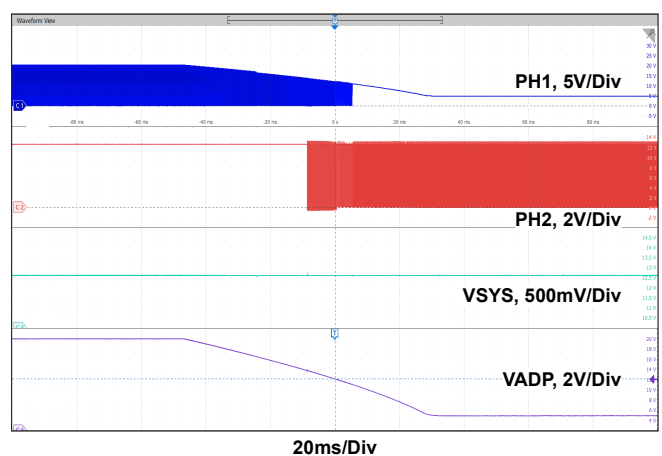


Figure 10. Adapter Voltage Ramps Down, Buck → Buck-Boost → Boost Operation Mode Transition

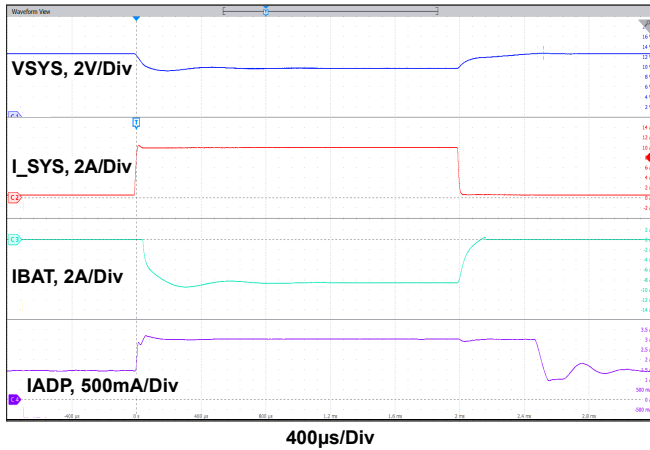


Figure 11. Boost Mode, Output Voltage Loop to Adapter Current Loop Transition. $V_{ADP} = 5V$, MaxSystemVoltage = 12.576V, $V_{BAT} = 11V$, System Load 0.5A to 10A Step, AdapterCurrentLimit = 3A, ChargeCurrent = 0A

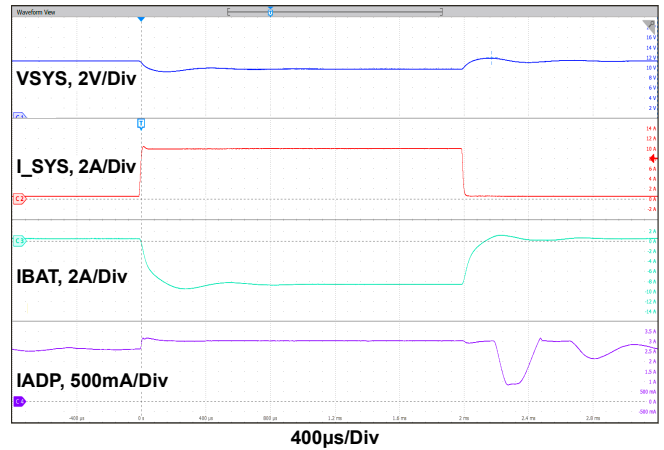


Figure 12. Boost Mode, Charging Current Loop to Adapter Current Loop Transition. $V_{ADP} = 5V$, MaxSystemVoltage = 12.576V, $V_{BAT} = 11V$, System Load 0.5A to 10A Step, AdapterCurrentLimit = 3A, ChargeCurrent = 0.5A

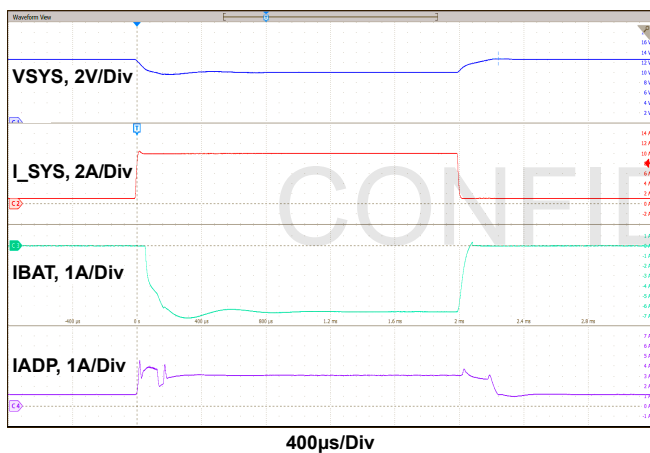


Figure 13. Buck-Boost Mode, Output Voltage Loop to Adapter Current Loop Transition. $V_{ADP} = 12V$, MaxSystemVoltage = 12.576V, $V_{BAT} = 11V$, System Load 1A to 10A Step, AdapterCurrentLimit = 3A, ChargeCurrent = 0A

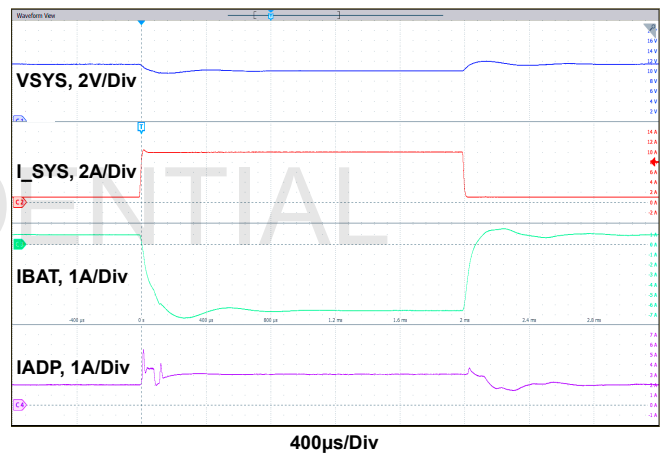


Figure 14. Buck-Boost Mode, Charging Current Loop to Adapter Current Loop Transition. $V_{ADP} = 12V$, MaxSystemVoltage = 12.576V, $V_{BAT} = 11V$, System Load 1A to 10A Step, AdapterCurrentLimit = 3A, ChargeCurrent = 1A

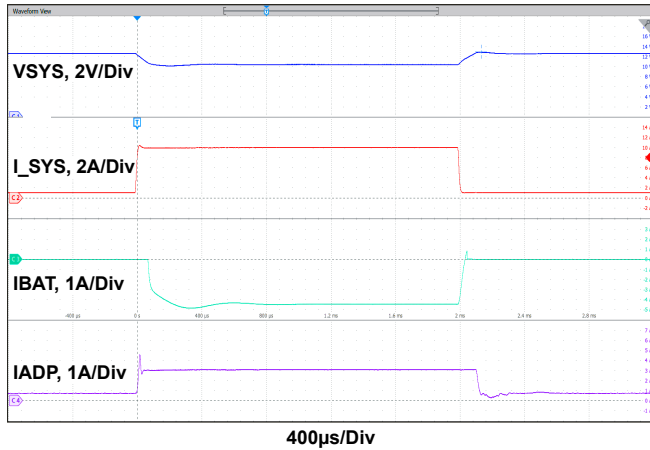


Figure 15. Buck Mode, Output Voltage Loop to Adapter Current Loop Transition. $V_{ADP} = 20V$, $MaxSystemVoltage = 12.576V$, $V_{BAT} = 11V$, System Load 1A to 10A Step, $AdapterCurrentLimit = 3A$, $ChargeCurrent = 0A$

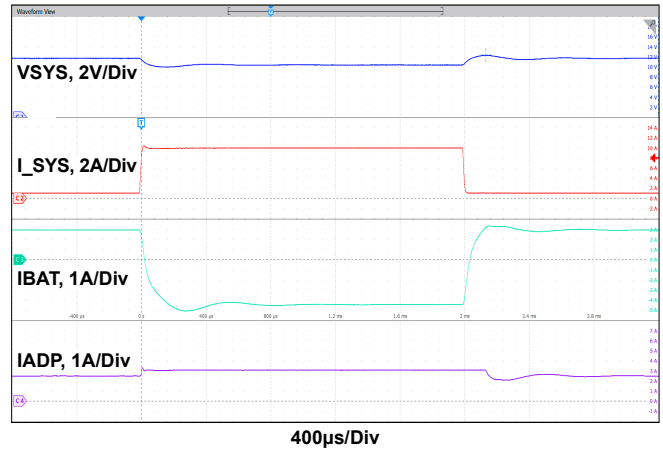


Figure 16. Buck Mode, Charging Current Loop to Adapter Current Loop Transition. $V_{ADP} = 20V$, $MaxSystemVoltage = 12.576V$, $V_{BAT} = 11V$, System Load 1A to 10A Step, $AdapterCurrentLimit = 3A$, $ChargeCurrent = 3A$

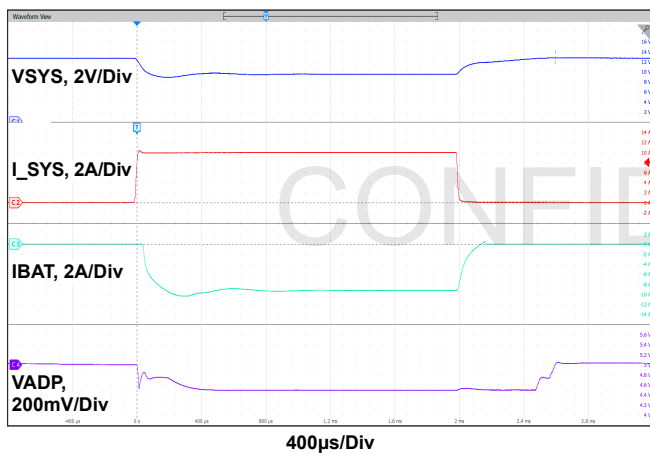


Figure 17. Boost Mode, Output Voltage Loop to Input Voltage Loop Transition. $V_{ADP} = 5.004V$, $MaxSystemVoltage = 12.576V$, $V_{BAT} = 11V$, $VINDAC = 4.437V$, System Load 0A to 10A Step, $ChargeCurrent = 0A$

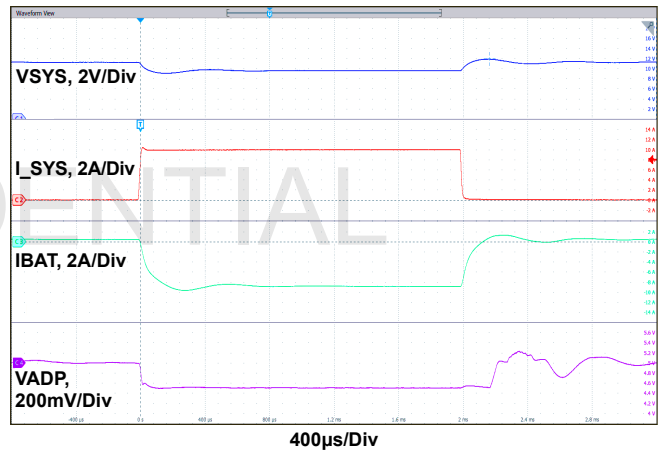


Figure 18. Boost Mode, Charging Current Loop to Input Voltage Loop Transition. $V_{ADP} = 5.004V$, $MaxSystemVoltage = 12.576V$, $V_{BAT} = 11V$, $VINDAC = 4.437V$, System Load 0A to 10A Step, $ChargeCurrent = 0.5A$

4. General SMBus Architecture

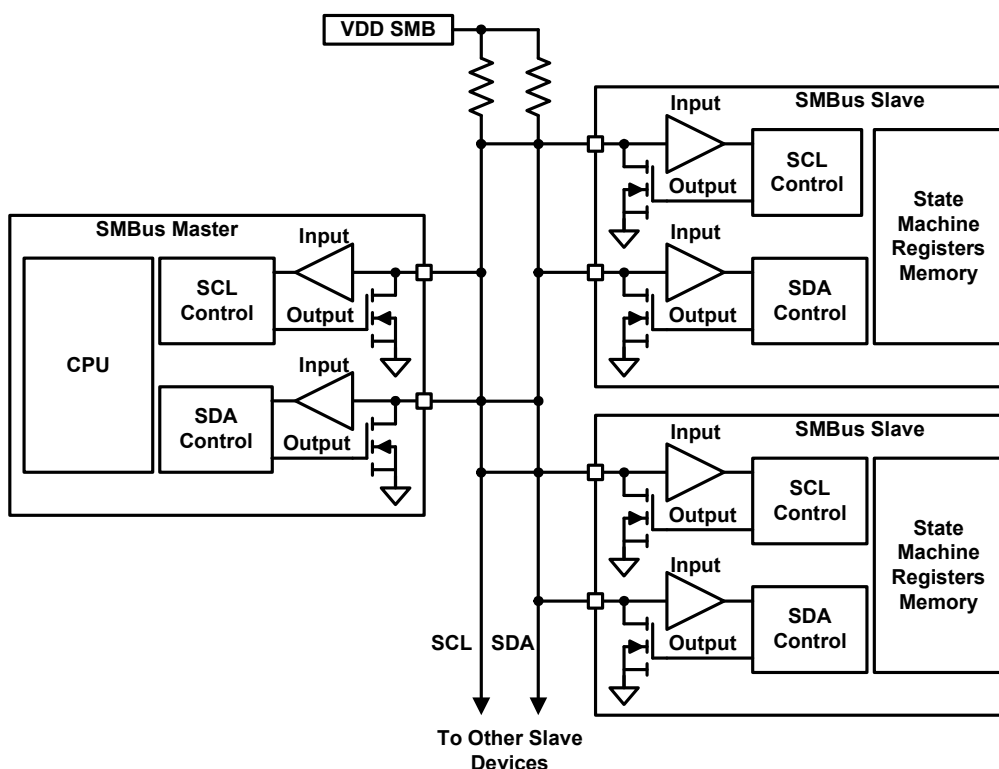


Figure 19. General SMBus

4.1 Data Validity

The data on the SDA line must be stable during the HIGH period of the SCL, unless generating a START or STOP condition. The HIGH or LOW state of the data line can change only when the clock signal on the SCL line is LOW. See [Figure 20](#).

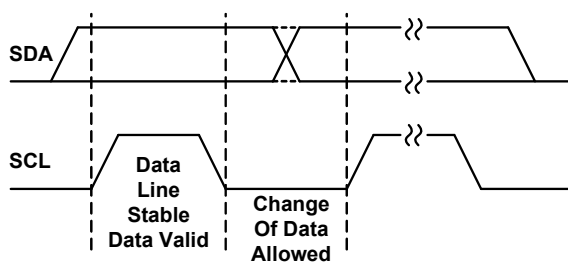


Figure 20. Data Validity

4.2 START and STOP Conditions

In [Figure 21](#), the START condition is a HIGH to LOW transition of the SDA line while SCL is HIGH.

The STOP condition is a LOW to HIGH transition on the SDA line while SCL is HIGH. A STOP condition must be sent before each START condition.

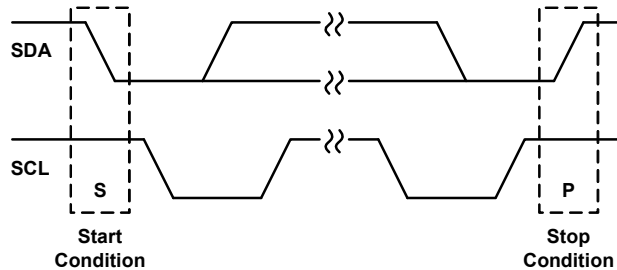


Figure 21. Start and Stop Waveforms

4.3 Acknowledge

Each address and data transmission uses nine clock pulses. The ninth pulse is the Acknowledge bit (ACK). After the start condition, the master sends seven slave address bits and a R/W bit during the next eight clock pulses. During the ninth clock pulse, the device that recognizes its own address holds the data line LOW to acknowledge (see [Figure 22](#)). Both the master and the slave use the ACK bit to acknowledge receipt of register addresses and data.

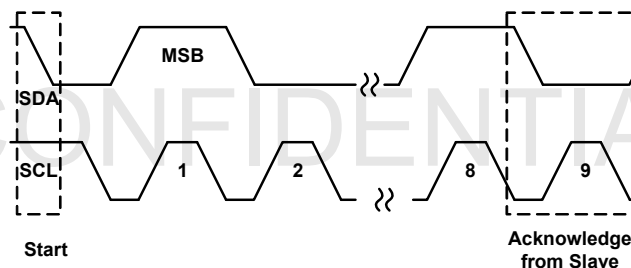


Figure 22. Acknowledge on the SMBus

4.4 SMBus Transactions

All transactions start with a control byte sent from the SMBus master device. The control byte begins with a Start condition followed by seven bits of slave address (0001001) and the R/W bit. The R/W bit is 0 for a WRITE or 1 for a READ. If any slave device on the SMBus bus recognizes its address, it acknowledges by pulling the Serial Data (SDA) line LOW for the last clock cycle in the control byte. If no slave exists at that address or it is not ready to communicate, the data line is 1 indicating a not acknowledge condition.

When the control byte is sent and the ISL9538C acknowledges it, the second byte sent by the master must be a register address byte such as 0x14 for the ChargeCurrent register. The register address byte tells the ISL9538C which register the master writes or reads. See [Table 2](#) for register details. When the ISL9538C receives a register address byte, it responds with an acknowledge.

4.5 Byte Format

Every byte on the SDA line must be eight bits long and must be followed by an ACK bit. Data is transferred with the Most Significant Bit (MSB) first and the Least Significant Bit (LSB) last. The LO Byte data is transferred before the HI Byte data. For example, when writing 0x41A0, 0xA0 is written first and 0x41 is written second.

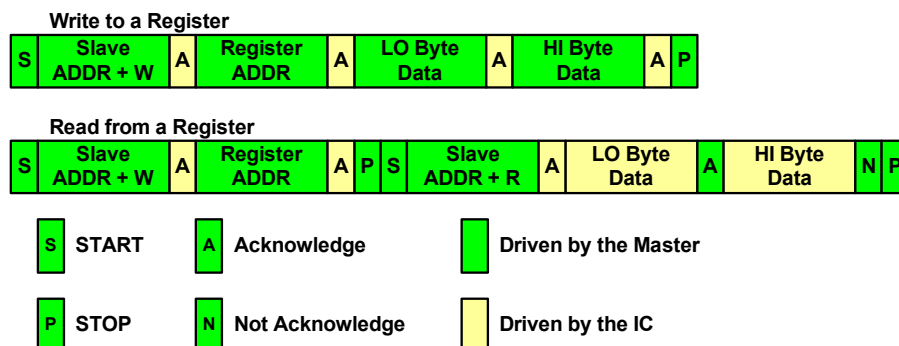


Figure 23. SMBus Read and Write Protocol

4.6 SMBus and I²C Compatibility

The ISL9538C SMBus minimum input logic high voltage is 1.3V, so it is compatible with an I²C with pull-up power supplies higher than 1.3V.

The ISL9538C SMBus registers are 16 bits, so it is compatible with either a 16-bit I²C or an 8-bit I²C with auto-increment capability.

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5. SMBus Commands

The ISL9538C receives control inputs from the SMBus interface after Power-On Reset (POR). The serial interface complies with the [System Management Bus Specification](#). The ISL9538C uses the SMBus Read-word and Write-word protocols (see [Figure 23](#)) to communicate with the host system and a smart battery. The ISL9538C is an SMBus slave device and does not initiate communication on the bus. It responds to the 7-bit address 0b0001001_ as follows:

The Read and Write address for the ISL9538C is:

- Read address = 0b00010011 (0X13H)
- Write address = 0b00010010 (0X12H)

The data (SDA) and clock (SCL) pins have Schmitt-trigger inputs that can accommodate slow edges. Choose pull-up resistors for SDA and SCL to achieve rise times according to the SMBus specifications.

The information in this datasheet is based on current sensing resistors $R_{S1} = 20\text{m}\Omega$ and $R_{S2} = 10\text{m}\Omega$, unless otherwise specified.

Table 2. Register Summary

Register Names	Register Address	Read/Write	Number Of Bits	Description	Default
ChargeCurrentLimit	0x14	R/W	11	[12:2] 11-bit, LSB size 4mA, total range 6080mA with 10m Ω R_{S2}	0A
MaxSystemVoltage	0x15	R/W	12	[14:3] 12-bit, LSB size 8mV, total range 18.304V	8.384V for 2-cell
					12.576V for 3-cell
					16.768V for 4-cell
Control5	0x38	R/W	16	Configures various charger options	0x0000h
Control0	0x39	R/W	16	Configures various charger options	0x0000h
Information1	0x3A	R	16	Indicates various charger statuses	0x0000h
AdapterCurrentLimit2	0x3B	R/W	11	[12:2] 11-bit, LSB size 4mA, total range 6080mA with 20m Ω R_{S1}	1500mA
Control1	0x3C	R/W	16	Configures various charger options	0x0000h
Control2	0x3D	R/W	16	Configures various charger options	0x0000h
MinSystemVoltage	0x3E	R/W	6	[13:8] 6-bit, LSB size 256mV, total range 13.824V	5.12V for 2-cell
					7.68V for 3-cell
					10.24V for 4-cell
AdapterCurrentLimit1	0x3F	R/W	11	[12:2] 11-bit, LSB size 4mA, total range 6080mA with 20m Ω R_{S1}	Set by PROG pin
Revision ID	0x44	R	8	Revision ID register - Read only	0x01h
ACProchot#	0x47	R/W	6	[12:7] Adapter current PROCHOT# threshold Default 3.072A, 128mA resolution for 20m Ω R_{S1} .	3.072A
DCProchot#	0x48	R/W	6	[13:8] Battery discharging current PROCHOT# threshold Default 4.096A, 256mA resolution for 10m Ω R_{S2} .	4.096A
V _{IN} Voltage	0x4B	R/W	6	[13:8] 6-bit, LSB size 341.3mV, total range 18.432mV V _{IN} loop voltage reference	4.096V
Control3	0x4C	R/W	16	Configures various charger options	0x0000h
Information2	0x4D	R	16	Indicates various charger statuses	0x0000h
Control4	0x4E	R/W	16	Configures various charger options	0x0000h
Control6	0x37	R/W	8	[7:0] 8-bit, configures various charger options	0x0000h or 0x0003h (Note 8)
Information3	0x90	R	1	[1] 1-bit, indicates pass-through mode status	0x0000h

Table 2. Register Summary (Continued)

Register Names	Register Address	Read/Write	Number Of Bits	Description	Default
Manufacturer ID	0xFE	R	8	Manufacturer ID register – 0x49 - Read only	0x0049h
Device ID	0xFF	R	8	Device ID register - 0x0C- Read only	0x000Ch

Note:

8. When inserting the battery for the first time, VSYS UV by default is 000 = Disabled. When inserting the adapter, VSYS UV threshold by default is 011 = 4.8V.

5.1 Setting the Charging Current Limit

To set the charging current limit, write a 16-bit ChargeCurrentLimit command (0x14H or 0b00010100) using the Write-word protocol shown in [Figure 23](#) and the data format shown in [Table 3](#) for a 10mΩ R_{S2} or [Table 4](#) for a 5mΩ R_{S2} .

The ISL9538C limits the charging current by limiting the CSOP-CSON voltage. By using the recommended current sense resistor values $R_{S1} = 20\text{m}\Omega$ and $R_{S2} = 10\text{m}\Omega$, the LSB of the register always translates to 4mA of charging current. The ChargeCurrentLimit register accepts any charging current command, but only the valid register bits are written to the register and the maximum value is clamped at 6080mA for $R_{S2} = 10\text{m}\Omega$.

The ChargeCurrentLimit register is reset to 0x0000H after POR. To set the battery charging current value, write a non-zero number to the ChargeCurrentLimit register. The ChargeCurrentLimit register can be read back to verify its content.

[Table 3](#) shows the conditions to enable fast charging according to the ChargeCurrentLimit register setting.

Table 3. ChargeCurrentLimit Register 0x14H (11-Bit, 4mA Step, 10mΩ Sense Resistor, x36)

Bit	Description
<1:0>	Not used
<2>	0 = Add 0mA of charge current limit 1 = Add 4mA of charge current limit
<3>	0 = Add 0mA of charge current limit 1 = Add 8mA of charge current limit
<4>	0 = Add 0mA of charge current limit 1 = Add 16mA of charge current limit
<5>	0 = Add 0mA of charge current limit 1 = Add 32mA of charge current limit
<6>	0 = Add 0mA of charge current limit 1 = Add 64mA of charge current limit
<7>	0 = Add 0mA of charge current limit 1 = Add 128mA of charge current limit
<8>	0 = Add 0mA of charge current limit 1 = Add 256mA of charge current limit
<9>	0 = Add 0mA of charge current limit 1 = Add 512mA of charge current limit
<10>	0 = Add 0mA of charge current limit 1 = Add 1024mA of charge current limit
<11>	0 = Add 0mA of charge current limit 1 = Add 2048mA of charge current limit
<12>	0 = Add 0mA of charge current limit 1 = Add 4096mA of charge current limit
<13:15>	Not used
Maximum	<12:2> = 10111110000 6080mA

Table 4. ChargeCurrentLimit Register 0x14H (11-Bit, 8mA Step, 5mΩ Sense Resistor, x36)

Bit	Description
<1:0>	Not used
<2>	0 = Add 0mA of charge current limit 1 = Add 8mA of charge current limit
<3>	0 = Add 0mA of charge current limit 1 = Add 16mA of charge current limit
<4>	0 = Add 0mA of charge current limit 1 = Add 32mA of charge current limit
<5>	0 = Add 0mA of charge current limit 1 = Add 64mA of charge current limit
<6>	0 = Add 0mA of charge current limit 1 = Add 128mA of charge current limit
<7>	0 = Add 0mA of charge current limit 1 = Add 256mA of charge current limit
<8>	0 = Add 0mA of charge current limit 1 = Add 512mA of charge current limit
<9>	0 = Add 0mA of charge current limit 1 = Add 1024mA of charge current limit
<10>	0 = Add 0mA of charge current limit 1 = Add 2048mA of charge current limit
<11>	0 = Add 0mA of charge current limit 1 = Add 4096mA of charge current limit
<12>	0 = Add 0mA of charge current limit 1 = Add 8192mA of charge current limit
<13:15>	Not used
Maximum	<12:2> = 10111110000 12160mA

5.2 Setting the Adapter Current Limit

To set the adapter current limit, write a 16-bit AdapterCurrentLimit1 command (0x3FH or 0b00111111) and/or AdapterCurrentLimit2 command (0x3BH or 0b00111011) using the Write-word protocol shown in [Figure 23](#) and the data format shown in [Table 5](#) for a 20mΩ R_{S1} or [Table 6](#) for a 10mΩ R_{S1} .

The ISL9538C limits the adapter current by limiting the CSIP-CSIN voltage. By using the recommended current sense resistor values, the LSB of the register always translates to 4mA of adapter current. Any adapter current limit command is accepted, but only the valid register bits are written to the AdapterCurrentLimit1 and AdapterCurrentLimit2 registers and the maximum value is clamped at 6080mA for $R_{S1} = 20\text{m}\Omega$.

After adapter POR, the AdapterCurrentLimit1 register is reset to the value programmed through the PROG pin resistor. The AdapterCurrentLimit2 register is set to its default value of 1.5A or keeps the value that is written to it previously if the battery is present first. The AdapterCurrentLimit1 and AdapterCurrentLimit2 registers can be read back to verify their content.

To set a second level adapter current limit, write a 16-bit AdapterCurrentLimit2 (0x3BH or 0b00111011) command using the Write-word protocol shown in [Figure 23](#) and the data format shown in [Table 5](#) for a 20mΩ R_{S1} or [Table 6](#) for a 10mΩ R_{S1} .

The AdapterCurrentLimit2 register has the same specification as the AdapterCurrentLimit1 register. See [Current Monitor](#) for detailed operation instructions.

Table 5. AdapterCurrentLimit1 Register 0x3FH and AdapterCurrentLimit2 Register 0x3BH (11-Bit, 4mA Step, 20mΩ Sense Resistor, x18)

Bit	Description
<1:0>	Not used
<2>	0 = Add 0mA of adapter current limit. 1 = Add 4mA of adapter current limit.
<3>	0 = Add 0mA of adapter current limit. 1 = Add 8mA of adapter current limit.
<4>	0 = Add 0mA of adapter current limit. 1 = Add 16mA of adapter current limit.
<5>	0 = Add 0mA of adapter current limit. 1 = Add 32mA of adapter current limit.
<6>	0 = Add 0mA of adapter current limit. 1 = Add 64mA of adapter current limit.
<7>	0 = Add 0mA of adapter current limit. 1 = Add 128mA of adapter current limit.
<8>	0 = Add 0mA of adapter current limit. 1 = Add 256mA of adapter current limit.
<9>	0 = Add 0mA of adapter current limit. 1 = Add 512mA of adapter current limit.
<10>	0 = Add 0mA of adapter current limit. 1 = Add 1024mA of adapter current limit.
<11>	0 = Add 0mA of adapter current limit. 1 = Add 2048mA of adapter current limit.
<12>	0 = Add 0mA of adapter current limit. 1 = Add 4096mA of adapter current limit.
<13:15>	Not used
Maximum	<12:4> = 10111110000 6080mA

Table 6. AdapterCurrentLimit1 Register 0x3FH and AdapterCurrentLimit2 Register 0x3BH (11-Bit, 8mA Step, 10mΩ Sense Resistor, x18)

Bit	Description
<1:0>	Not used
<2>	0 = Add 0mA of adapter current limit. 1 = Add 8mA of adapter current limit.
<3>	0 = Add 0mA of adapter current limit. 1 = Add 16mA of adapter current limit.
<4>	0 = Add 0mA of adapter current limit. 1 = Add 32mA of adapter current limit.
<5>	0 = Add 0mA of adapter current limit. 1 = Add 64mA of adapter current limit.
<6>	0 = Add 0mA of adapter current limit. 1 = Add 128mA of adapter current limit.
<7>	0 = Add 0mA of adapter current limit. 1 = Add 256mA of adapter current limit.
<8>	0 = Add 0mA of adapter current limit. 1 = Add 512mA of adapter current limit.
<9>	0 = Add 0mA of adapter current limit. 1 = Add 1024mA of adapter current limit.
<10>	0 = Add 0mA of adapter current limit. 1 = Add 2048mA of adapter current limit.
<11>	0 = Add 0mA of adapter current limit. 1 = Add 4096mA of adapter current limit.

Table 6. AdapterCurrentLimit1 Register 0x3FH and AdapterCurrentLimit2 Register 0x3BH (11-Bit, 8mA Step, 10mΩ Sense Resistor, x18) (Continued)

Bit	Description
<12>	0 = Add 0mA of adapter current limit. 1 = Add 8192mA of adapter current limit.
<13:15>	Not used
Maximum	<12:4> = 10111110000 12160mA

5.3 Setting the Two-Level Adapter Current Limit Duration

For a two-level adapter current limit, write a 16-bit T1 and T2 command (0x38H or 0b00111000) using the Write-word protocol shown in [Figure 23](#) and the data format shown in [Table 5](#) or [Table 6](#) to set the AdapterCurrentLimit1 duration t1. Write a 16-bit T2 command (0x38H or 0b00111000) to set AdapterCurrentLimit2 duration t2. The T1 and T2 registers accept any command, but only the valid register bits are written. See [Current Monitor](#) for detailed operation instructions.

Table 7. Control5 0x38H

Bit	Description
<2:0> T1	000 = 10ms (default) 001 = 20ms 010 = 15ms 011 = 5ms 100 = 1ms 101 = 0.5ms 110 = 0.1ms 111 = 0ms
<10:8> T2	000 = 10μs (default) 001 = 100μs 010 = 500μs 011 = 1ms 100 = 300μs 101 = 750μs 110 = 2ms 111 = 10ms

5.4 Setting the Maximum Charging Voltage or System Regulating Voltage

To set the maximum charging voltage or the system regulating voltage, write a 16-bit MaxSystemVoltage command (0x15H or 0b00010101) using the Write-word protocol shown in [Figure 23](#) and the data format shown in [Table 8](#).

The maximum system voltage range is 8mV to 18.304V. The MaxSystemVoltage register accepts any voltage command, but only the valid register bits are written to the register and the maximum value is clamped at 18.304V. The ISL9538C accepts a 0V command, but the register value does not change.

The MaxSystemVoltage register sets the battery full charging voltage limit. The MaxSystemVoltage register setting is also the system bus voltage regulation point when the battery is absent, or if the battery is present but is not in Charging mode. See [System Voltage Regulation and Trickle Charging](#) for details.

The VSYS pin senses the battery voltage for maximum charging voltage regulation. The VSYS pin is also the system bus voltage regulation sense point.

Table 8. MaxSystemVoltage Register 0x15H (8mV Step)

Bit	Description
<2:0>	Not used
<3>	0 = Add 0mV of charge voltage. 1 = Add 8mV of charge voltage.
<4>	0 = Add 0mV of charge voltage. 1 = Add 16mV of charge voltage.

Table 8. MaxSystemVoltage Register 0x15H (8mV Step) (Continued)

Bit	Description
<5>	0 = Add 0mV of charge voltage. 1 = Add 32mV of charge voltage.
<6>	0 = Add 0mV of charge voltage. 1 = Add 64mV of charge voltage.
<7>	0 = Add 0mV of charge voltage. 1 = Add 128mV of charge voltage.
<8>	0 = Add 0mV of charge voltage. 1 = Add 256mV of charge voltage.
<9>	0 = Add 0mV of charge voltage. 1 = Add 512mV of charge voltage.
<10>	0 = Add 0mV of charge voltage. 1 = Add 1024mV of charge voltage.
<11>	0 = Add 0mV of charge voltage. 1 = Add 2048mV of charge voltage.
<12>	0 = Add 0mV of charge voltage. 1 = Add 4096mV of charge voltage.
<13>	0 = Add 0mV of charge voltage. 1 = Add 8192mV of charge voltage.
<14>	0 = Add 0mV of charge voltage. 1 = Add 16384mV of charge voltage.
<15>	Not used
Maximum	18304mV

5.5 Setting the Minimum System Voltage

To set the minimum system voltage, write a 16-bit MinSystemVoltage command (0x3EH or 0b00111110) using the Write-word protocol shown in [Figure 23](#) and the data format shown in [Table 9](#).

The minimum system voltage range is 256mV to 13.824V. The MinSystemVoltage register accepts any voltage command, but only the valid register bits are written to the register. Set the MinSystemVoltage register value lower than the MaxSystemVoltage register value and the maximum value is clamped at 13.824V.

The MinSystemVoltage register sets the battery voltage threshold for entry and exit of Trickle Charging mode and for entry and exit of Learn mode. The VBAT pin senses the battery voltage to compare with the MinSystemVoltage register setting. See [Battery Learn Mode](#) for details.

The MinSystemVoltage register setting is also the system voltage regulation point when it is in Trickle Charging mode. The VSYS pin is the system voltage regulation sense point in Trickle Charging mode. See [System Voltage Regulation and Trickle Charging](#) for details.

Table 9. MinSystemVoltage Register 0x3EH

Bit	Description
<7:0>	Not used
<8>	0 = Add 0mV of charge voltage. 1 = Add 256mV of charge voltage.
<9>	0 = Add 0mV of charge voltage. 1 = Add 512mV of charge voltage.
<10>	0 = Add 0mV of charge voltage. 1 = Add 1024mV of charge voltage.
<11>	0 = Add 0mV of charge voltage. 1 = Add 2048mV of charge voltage.

Table 9. MinSystemVoltage Register 0x3EH (Continued)

Bit	Description
<12>	0 = Add 0mV of charge voltage. 1 = Add 4096mV of charge voltage.
<13>	0 = Add 0mV of charge voltage. 1 = Add 8192mV of charge voltage.
<15:14>	Not used
Maximum	13824mV

5.6 Setting the PROCHOT# Threshold for Adapter Overcurrent Conditions

To set the PROCHOT# assertion threshold for adapter overcurrent conditions, write a 16-bit ACProchot# command (0x47H or 0b01000111) using the Write-word protocol shown in [Table 23](#) and the data format shown in [Table 10](#). By using the recommended current sense resistor values, the LSB of the register always translates to 128mA of adapter current. The ACProchot# register accepts any current command, but only the valid register bits are written to the register and the maximum value is clamped at 6400mA for $R_{S1} = 20m\Omega$.

After POR, the ACProchot# register is reset to 0x0C00H. The ACProchot# register can be read back to verify its content.

If the adapter current exceeds the ACProchot# register setting, the PROCHOT# signal asserts after the debounce time programmed by the Control2 register Bit<10:9> and latches on for the minimum time programmed by Control2 register Bit<8:6>.

Table 10. ACProchot# Register 0x47H (20mΩ Sensing Resistor, 128mA SteP, x18 Gain)

Bit	Description
<6:0>	Not used
<7>	0 = Add 0mA of ACProchot# threshold. 1 = Add 128mA of ACProchot# threshold.
<8>	0 = Add 0mA of ACProchot# threshold. 1 = Add 256mA of ACProchot# threshold.
<9>	0 = Add 0mA of ACProchot# threshold. 1 = Add 512mA of ACProchot# threshold.
<10>	0 = Add 0mA of ACProchot# threshold. 1 = Add 1024mA of ACProchot# threshold.
<11>	0 = Add 0mA of ACProchot# threshold. 1 = Add 2048mA of ACProchot# threshold.
<12>	0 = Add 0mA of ACProchot# threshold. 1 = Add 4096mA of ACProchot# threshold.
<15:13>	Not used
Maximum	<12:7> = 110010, 6400mA

5.7 Setting the PROCHOT# Threshold for the Battery Over Discharging Current Condition

To set the PROCHOT# signal assertion threshold for the battery over discharging current condition, write a 16-bit DCProchot# command (0x48H or 0b01001000) using the Write-word protocol shown in [Figure 23](#) and the data format shown in [Table 11](#). By using the recommended current sense resistor values, the LSB of the register always translates to 256mA of adapter current. The DCProchot# register accepts any current command, but only the valid register bits are written to the register and the maximum value is clamped at 12.8A for $R_{S2} = 10m\Omega$.

After POR, the DCProchot# register is reset to 0x1000H. The DCProchot# register can be read back to verify its content.

If the battery discharging current exceeds the DCProchot# register setting, the PROCHOT# signal asserts after the debounce time programmed by the Control2 register Bit<10:9> and latches on for the minimum time programmed by Control2 register Bit<8:6>.

In Battery Only mode and Low Power mode, the DCProchot# threshold is set by Control0 register Bit<4:3>.

In Battery Only mode, the DCProchot# function works only when PSYS is enabled, because enabling PSYS activates the internal comparator reference. The Information register Bit<15> indicates whether the internal comparator reference is active. When the adapter is present, the internal comparator reference is always active.

Table 11. DCProchot# Register 0x48H (10mΩ Sensing Resistor, 256mA Step, x18 Gain)

Bit	Description
<7:0>	Not used
<8>	0 = Add 0mA of DCProchot# threshold. 1 = Add 256mA of DCProchot# threshold.
<9>	0 = Add 0mA of DCProchot# threshold. 1 = Add 512mA of DCProchot# threshold.
<10>	0 = Add 0mA of DCProchot# threshold. 1 = Add 1024mA of DCProchot# threshold.
<11>	0 = Add 0mA of DCProchot# threshold. 1 = Add 2048mA of DCProchot# threshold.
<12>	0 = Add 0mA of DCProchot# threshold. 1 = Add 4096mA of DCProchot# threshold.
<13>	0 = Add 0mA of DCProchot# threshold. 1 = Add 8192mA of DCProchot# threshold.
<15:14>	Not used.
Maximum	<13:8> = 110010, 12800mA

5.8 Setting the PROCHOT# Debounce Time and Duration Time

Control2 register Bit<10:9> configures the PROCHOT# signal debounce time before its assertion for ACProchot# and DCProchot#. The low system voltage PROCHOT# has a fixed debounce time of 8μs.

Control2 register Bit<8:6> configures the minimum duration of the PROCHOT# signal when asserted.

5.9 Setting the Control Registers

The Control0, Control1, Control2, Control3, Control4, Control5, and Control6 registers configure the ISL9538C operation. To change certain functions or options after POR, write control commands to any of the following control registers using the Write-word protocol shown in [Figure 23](#) and the data format shown in [Table 12](#), [Table 13](#), [Table 14](#), [Table 15](#), [Table 16](#), [Table 17](#), and [Table 18](#), respectively.

- 16-bit control command to the Control0 register (0x39H or 0b00111001)
- 16-bit control command to the Control1 register (0x3CH or 0b00111100)
- 16-bit control command to the Control2 register (0x3DH or 0b00111101)
- 16-bit control command to the Control3 register (0x4CH or 0b00111100)
- 16-bit control command to the Control4 register (0x4EH or 0b00111101)
- 16-bit control command to the Control5 register (0x38H or 0b00111000)
- 8-bit control command to the control6 register (0x37H or 0b00110111)

Table 12. Control0 Register 0x39H

Bit	Bit Name	Description
<15:13>	Forward Buck Phase Comparator Threshold Offset	Bit<15:13> adjusts the phase comparator threshold offset for forward buck and buck-boost. 000 = 0mV 001 = 1mV 010 = 2mV 011 = 3mV 100 = -4mV 101 = -3mV 110 = -2mV 111 = -1mV

Table 12. Control0 Register 0x39H (Continued)

Bit	Bit Name	Description																				
<12:10>	Forward Boost Phase Comparator Threshold Offset	Bit<12:10> adjusts the phase comparator threshold offset for forward boost. 000 = 0mV 001 = 0.5mV 010 = 1mV 011 = 1.5mV 100 = -2mV 101 = -1.5mV 110 = -1mV 111 = -0.5mV																				
<9,8,0>	Not Used	Not used																				
<7>	SMBus Timeout	The ISL9538C includes a timer to ensure the SMBus master is active and to prevent overcharging the battery. If the adapter is present and if the ISL9538C does not receive a write to the MaxChargeVoltage or ChargeCurrentLimit register within 175s, the ISL9538C terminates charging. If a timeout occurs, writing the MaxChargeVoltage or ChargeCurrentLimit register re-enables charging. 0 = Enable the SMBus timeout function 1 = Disable the SMBus timeout function																				
<6:5>	High-Side FET Short Detection Threshold	Bit<6:5> configures the high-side FET short detection PHASE node voltage threshold while the low-side FET turns on. 00 = 400mV (default) 01 = 500mV 10 = 600mV 11 = 800mV																				
<4:3>	DCProchot# Threshold in Battery Only Low Power Mode	Bit<4:3> only configures the battery discharging current DCProchot# threshold in battery only Low Power mode indicated by Information1 register 0x3A Bit<15>. If PSYS is enabled, the battery discharge current DCProchot# threshold is set by the DCProchot# register 0x48 setting. <table><tr><th>Bit<4:3></th><th>R_{s2} = 10mΩ (A)</th><th>R_{s2} = 20mΩ (A)</th><th>R_{s2} = 5mΩ (A)</th></tr><tr><td>00</td><td>12 (Default)</td><td>6</td><td>24</td></tr><tr><td>01</td><td>10</td><td>5</td><td>20</td></tr><tr><td>10</td><td>8</td><td>4</td><td>16</td></tr><tr><td>11</td><td>6</td><td>3</td><td>12</td></tr></table>	Bit<4:3>	R _{s2} = 10mΩ (A)	R _{s2} = 20mΩ (A)	R _{s2} = 5mΩ (A)	00	12 (Default)	6	24	01	10	5	20	10	8	4	16	11	6	3	12
Bit<4:3>	R _{s2} = 10mΩ (A)	R _{s2} = 20mΩ (A)	R _{s2} = 5mΩ (A)																			
00	12 (Default)	6	24																			
01	10	5	20																			
10	8	4	16																			
11	6	3	12																			
<2>	Input Voltage Regulation Loop	Bit<2> disables or enables the input voltage regulation loop. 0 = Enable the input voltage regulation loop (default) 1 = Disable the input voltage regulation loop																				
<1>	Force Buck Mode	Bit<1> disables or enables Force Buck mode. If the Force Buck mode bit is enabled, the Buck-Boost window narrows. 0 = Disable Force Buck mode (default) 1 = Enable Force Buck mode																				

Table 13. Control1 Register 0x3CH

Bit	Bit Name	Description
<15:14>	General Purpose Comparator Assertion Debounce Time	Bit<15:14> configures the general purpose comparator assertion debounce time. 00 = 2 μ s (default) 01 = 12 μ s 10 = 2ms 11 = 5s
<13>	Exit Learn Mode Option	Bit<13> provides the option to Exit Learn mode when the battery voltage is lower than the MinSystemVoltage register setting. 0 = Stay in Learn mode even if V _{BAT} < MinSystemVoltage register setting (default) 1 = Exit Learn mode if V _{BAT} < MinSystemVoltage register setting
<12>	Learn Mode	Bit<12> enables or disables Battery Learn mode. 0 = Disable Battery Learn mode (default) 1 = Enable Battery Learn mode To enter Learn mode, the BATGONE pin must be low, that is, the battery must be present.
<11>	Not Used	Not used. When writing, write a 0.
<10>	Audio Filter	Bit<10> enables or disables the audio filter function. 0 = Disable the audio filter function (default) 1 = Enable the audio filter function
<9:8>	Switching Frequency	Bit<9:8> configures the switching frequency and overrides the switching frequency set by the PROG pin. 00 = Switching frequency set by the PROG pin (default) 01 = 839kHz 10 = 723kHz 11 = 635kHz To keep the switching frequency set by the PROG pin resistor, leave Bit<9:8> as it is or write code 00, which sets the same frequency as the PROG pin resistor does.
<7>	Not Used	Not used.
<6>	Turbo	Bit<6> enables or disables Turbo mode. When the turbo function is enabled, the BGATE FET turns on in Turbo mode. See Table 24 for the BGATE ON/OFF truth table. 0 = Enable Turbo mode (default) 1 = Disable Turbo mode
<5>	AMON/BMON Function	Bit<5> enables or disables the current monitor function AMON and BMON. 0 = Enable AMON/BMON (default) 1 = Disable AMON/BMON Bit<5> is only valid in Battery Only mode. When the adapter is present, AMON/BMON is automatically enabled and Bit<5> becomes invalid.
<4>	AMON or BMON	Bit<4> selects AMON or BMON as the AMON/BMON pin output. 0 = AMON (default) 1 = BMON
<3>	PSYS	Bit<3> enables or disables the system power monitor PSYS function. 0 = Disables the PSYS function (default) 1 = Enables the PSYS function
<2>	VSYS	Bit<2> enables or disables the buck-boost charger switching VSYS output. When disabled, the ISL9538C stops switching and forces the BGATE FET on. 0 = Enables VSYS output (default) 1 = Disables VSYS output
<1:0>	Low_VSYS_Prochot# Reference	Bit<1:0> configures the Low_VSYS_Prochot# assertion threshold. 00 = 6.0V (default) 01 = 6.3V 10 = 6.6V 11 = 6.9V

Table 14. Control2 Register 0x3DH

Bit	Bit Name	Description
<15:14>	Trickle Charging Current	Bit<15:14> configures the charging current in Trickle Charging mode. 00 = 256mA (default) 01 = 128mA 10 = 64mA 11 = 512mA
<13>	Not Used	Not used
<12>	Two-Level Adapter Current Limit Function	Bit<12> enables or disables the two-level adapter current limit function. 0 = Disables the current limit function (default) 1 = Enables the current limit function
<11>	Adapter Insertion to Switching Debounce	Bit<11> configures the debounce time from adapter insertion to when ACOK is asserted high. 0 = 1.3s (default) 1 = 150ms After VDD POR, for the first time the adapter is plugged in, the ASGATE turn-on delay is always 150ms, regardless of the Bit<11> setting. This bit sets the ASGATE turn-on delay only after ASGATE turns off at least one time when VDD is above its POR value and the Bit<11> default is 0 for 1.3s.
<10:9>	Prochot# Debounce	Bit<10:9> configures the Prochot# debounce time before its assertion for ACProchot# and DCProchot#. 00: 7μs (default) 01: 100μs 10: 500μs 11: 1ms The Low_VSYS_Prochot# has a fixed 8μs debounce time.
<8:6>	Prochot# Duration	Bit<8:6> configures the minimum duration of the PROCHOT# signal when asserted. 000 = 10ms (default) 001 = 20ms 010 = 15ms 011 = 5ms 100 = 1ms 101 = 500μs 110 = 100μs 111 = 0s
<5>	Not Used	Not used
<4>	CMIN Reference	Bit<4> configures the general purpose comparator reference voltage. 0 = 1.2V (default) 1 = 2V
<3>	General Purpose Comparator	Bit<3> enables or disables the general purpose comparator. 0 = Enable the general purpose comparator (default) 1 = Disable the general purpose comparator
<2>	CMOUT Polarity	Bit<2> configures the general purpose comparator output polarity when asserted. The comparator reference voltage is connected at the inverting input node. 0 = CMOUT is High when CMIN is higher than reference (default) 1 = CMOUT is Low when CMIN is higher than reference
<1>	Not Used	Not Used
<0>	Pass-Through Mode	Bit<0> enables or disables Pass-Through mode. 0 = Disable Pass-Through mode (default) 1 = Enable Pass-Through mode

Table 15. Control3 Register 0x4CH

Bit	Bit Name	Description
<15>	Reread PROG Pin Resistor	Bit<15> specifies whether to reread the PROG pin resistor. 0 = Reread PROG pin resistor 1 = Do not reread PROG pin resistor
<14>	Reload ACLIM When Adapter Is Plugged In	Bit<14> reloads the AdapterCurrentLimit1 register set by the PROG pin resistor. 0 = Reload the AdapterCurrentLimit1 register 1 = Do not reload the AdapterCurrentLimit1 register
<13>	Autonomous Charging Termination Time	Bit<13> configures the autonomous charging termination time. 0 = 20ms 1 = 200ms
<12:11>	Charger Timeout	Bit<12:11> configures the SMBus charger timeout time. 00 = 175s (default) 01 = 87.5s 10 = 43.75s 11 = 5s
<10>	BGATE OFF	Bit<10> enables or disables Battery Ship mode. 0 = Idle 1 = Force BGATE MOSFET off (enable Battery Ship mode)
<9>	PSYS Gain	Bit<9> configures the system power monitor PSYS output gain. 0 = 1.467 μ A/W (default) 1 = 0.734 μ A/W
<8>	Exit IDM Timer	Bit<8> configures the Ideal Diode mode exit timer when the battery discharge current is less than 200mA. 0 = 40ms (default) 1 = 80ms
<7>	Autonomous Charging Mode	Bit<7> enables Autonomous Charging mode. 0 = Enable Autonomous Charging mode 1 = Battery charging current control through SMBus
<6>	AC and CC Feedback Gain	Bit<6> configures AC and CC feedback gain for high current. 0 = Idle 1 = x0.5
<5>	Input Current Limit Loop	Bit<5> disables the input current limit loop. 0 = Enable input current limit loop 1 = Disable input current limit loop
<4>	Input Current Limit Loop when BATGONE = 1	Bit<4> disables the input current limit loop when BATGONE = 1. 0 = Enable ACLIM when BATGONE = 1 1 = Disable ACLIM when BATGONE = 1
<3>	AMON/BMON Direction	Bit<3> configures the AMON/BMON direction. 0 = Adapter current monitor/battery charging current monitor 1 = Battery discharging current monitor
<2>	Digital Reset	Bit<2> resets all SMBus register values to the POR default value. 0 = Idle 1 = Reset
<1>	Buck-Boost Stretch CCM Period	Buck-boost stretch CCM period (T2 TIME). See Control4 Bit<8> on page 36 . Control3<1> Control4<8> 00 = 2x (default) 01 = 3x 10 = 1x 11 = 0.6x
<0>	Not Used	Not used

Table 16. Control4 Register 0x4EH

Bit	Bit Name	Description
<15:14>	Dither Enable	Bit<15:14> enables the switching frequency dithering function. 00 = Disable dither (default) 01 = Dither 100 - 102% 10 = Dither 100 - 104% 11 = Dither 100 - 106%
<13>	ADP Side Discharge	Bit<13> enables or disables the ADP side discharge function. Typical 15mA. 0 = Disable ADP side discharge function (default) 1 = Enable ADP discharge function
<12>	VSYS Sink	Bit<12> enables or turns on the discharge FET to pull down the VSYS. 0 = Disable, 10mA sink turned off (default) 1 = Enable, 10mA sink turned on
<11>	BGATE Tri-state	Bit<11> enables or disables the BGATE tri-state function. 0 = Disable BGATE tri-state (default) 1 = Enable BGATE tri-state
<10>	Not Used	Not used.
<9>	T2DCM	Buck-Boost T2 time in DCM (T2DCM), reduces input ripple. 0 = Reduced T2 time (increases switching frequency in DCM) (default) 1 = Normal T2 time
<8>	Buck-Boost Stretch CCM Period	Buck-Boost stretch CCM period (T2 TIME). See Control3 Bit<1> on page 35 . Control3<1> Control4<8> 00 = 2x (default) 01 = 3x 10 = 1x 11 = 0.6x
<7>	Not Used	Not used. When writing, write 0.
<6>	BATGONE PROCHOT#	Bit<6> enables or disables trigger PROCHOT# with BATGONE. 0 = Disable trigger PROCHOT# with BATGONE 1 = Enable trigger PROCHOT# with BATGONE
<5>	ACOK PROCHOT#	Bit<5> enables or disables trigger PROCHOT# with ACOK. 0 = Disable trigger PROCHOT# with ACOK 1 = Enable trigger PROCHOT# with ACOK
<4>	Comparator PROCHOT#	Bit<4> enables or disables trigger PROCHOT# with general purpose comparator rising. 0 = Disable trigger PROCHOT# with general purpose comparator rising 1 = Enable trigger PROCHOT# with general purpose comparator rising
<3:2>	ACOK falling or BATGONE Rising Debounce	Bit<3:2> configures the debounce time from ACOK falling or BATGONE rising to PROCHOT# trip. 00 = 2μs 01 = 25μs 10 = 125μs 11 = 250μs
<1>	PROCHOT# Clear	Bit<1> clears PROCHOT#. 0 = Idle 1 = Clear PROCHOT#
<0>	PROCHOT# Latch	Bit<0> manually resets PROCHOT#. 0 = PROCHOT# signal auto-clear 1 = Hold PROCHOT# low when tripped

Table 17. Control5 Register 0x38H

Bit	Bit Name	Descriptions
<15>	Not Used	Not used
<14>	Not Used	Not used
<13:12>	Not Used	Not used
<11>	Not Used	Not used
<10:8>	T2 (Two level ACLIM enabled)	Bit<10:8> sets the time corresponding to AdapterCurrentLimit2. 000 = 10μs (default) 001 = 100μs 010 = 500μs 011 = 1ms 100 = 300μs 101 = 750μs 110 = 2ms 111 = 10ms
<7:6>	Not used	Not used
<5>	Not Used	Not used
<4>	Not Used	Not used
<3>	Not Used	Not used
<2:0>	T1 (Two level ACLIM enabled)	Bit<2:0> sets the time corresponding to AdapterCurrentLimit1. 000 = 10ms (default) 001 = 20ms 010 = 15ms 011 = 5ms 100 = 1ms 101 = 0.5ms 110 = 0.1ms 111 = 0ms

Table 18. Control6 Register 0x37H

Bit	Bit Name	Description
<15:8>	Not Used	Not used
<7>	Turn off BGATE at VSYSOV	Bit<7> turns off BGATE during VSYSOV 0 = No action 1 = Turn off BGATE
<6>	Charge Current and Maximum System Voltage Slew Rate (1 LSB/clock) (Note 9)	Bit<6> enables the charger current and maximum system voltage slew rate control. 0 = Disable the charger current and maximum system voltage slew rate control (default) 1 = Enable the charger current and maximum system voltage slew rate control
<5>	Not Used	Not used
<4>	CMOUT Latch Data/Clear	When CMOUT Latch is enabled with Ctrl6<3> = 0, the CMOUT Latch data can be read from Bit<4>, and can be cleared to the current CMOUT data value by writing Bit<4> = 1. Read: CMOUT Latched Data Value Write 1 to clear CMOUT data to the current value.
<3>	CMOUT Latch	Bit<3> enables the CMOUT latch function. 1 = Disable the CMOUT latch function 0 = Enable the CMOUT latch function (default)
<2:0>	VSYS Undervoltage Threshold (Note 10)	Bit<2:0> set VSYS under voltage threshold. 000 = Disable 001 = 3.0V 010 = 3.9V 011 = 4.8V (default) 100 = 5.7V 101 = 6.6V 110 = 7.5V 111 = 8.4V

Note:

- Typical values of 1LSB/clock slew rate: 8mV/μs for system voltage, and 4mA/μs for charging current with 10mΩ sense resistor.
- When inserting the battery for the first time, VSYS UV by default is 000 = Disabled. When inserting the adapter, VSYS UV threshold by default is 011 = 4.8V.

5.10 Input Voltage Register

The Input Voltage register contains SMBus readable and writable input voltage limits. The default is 4.096V. This register accepts any current command, but only the valid register bits are written to the register and the maximum value is clamped at 18.432V.

Table 19. Input Voltage Register 0x4BH

Bit	Description
<7:0>	Not used
<8>	0 = Add 0mV of input voltage 1 = Add 341.3mV of input voltage
<9>	0 = Add 0mA of input voltage 1 = Add 682.6mV of input voltage
<10>	0 = Add 0mV of input voltage 1 = Add 1365.3mV of input voltage
<11>	0 = Add 0mV of input voltage 1 = Add 2730.6mV of input voltage
<12>	0 = Add 0mV of input voltage 1 = Add 5461.3mV of input voltage
<13>	0 = Add 0mV of input voltage 1 = Add 10922.6mV of input voltage
<15:14>	Not used
Maximum	18432mV

5.11 Information Register

The Information register contains SMBus readable information about manufacturing and Operating modes. [Table 20](#), [Table 21](#), and [Table 22](#) identify the bit locations of the information available.

Table 20. Information1 Register 0x3AH

Bit	Description
<3:0>	Not used
<4>	Bit<4> indicates whether the Trickle Charging mode is active. 0 = Trickle Charging mode is not active 1 = Trickle Charging mode is active
<9:5>	Not used
<10>	Bit<10> indicates whether the Low_VSYS_Prochot# is tripped. 0 = Low_VSYS Prochot# is not tripped 1 = Low_VSYS Prochot# is tripped
<11>	Bit<11> indicates whether DCProchot# is tripped. 0 = DCProchot# is not tripped 1 = DCProchot# is tripped
<12>	Bit<12> indicates whether ACProchot# is tripped. 0 = ACProchot# is not tripped 1 = ACProchot# is tripped
<14:13>	Bit<14:13> indicates the active control loop. 00 = MaxSystemVoltage control loop is active 01 = Charging current loop is active 10 = Adapter current limit loop is active 11 = Input voltage loop is active
<15>	Bit<15> indicates whether the internal reference circuit is active. Bit<15> = 0 indicates that the ISL9538C is in Low Power mode. 0 = Reference is not active 1 = Reference is active

Table 21. Information2 Register 0x4DH

Bit	Description
<4:0>	Program Resister read out Battery cell number Switching frequency Adapter current limit
<7:5>	Bit<7:5> indicates the ISL9538C operation mode. 001 = Boost Mode 010 = Buck Mode 011 = Buck-Boost Mode
<11:8>	Bit<11:8> indicates the ISL9538C state machine status. 0000 = OFF 0001 = BATTERY 0010 = ADAPTER 0011 = ACOK 0100 = VSYS 0101 = CHARGE 0110 = Not Applicable 0111 = Not Applicable 1000 = ENLDO5 1001 = Not Applicable 1010 = TRIM/ENCHREF 1011 = ACHRG 1100 = CAL 1101 = AGON/AGONTG 1110 = WAIT/PSYS 1111 = ADPPSYS
<12>	Bit<10> indicates the BATGONE pin status. 0 = Battery is present 1 = No battery
<13>	Bit<11> indicates the general purpose comparator output after debounce time. 0 = Comparator output is low 1 = Comparator output is high
<14>	Bit<12> indicates the ACOK pin status. 0 = No adapter 1 = Adapter is present
<15>	Not used

Table 22. Information3 Register 0x90H

Bit	Description
<15:2>	Not used
<1>	Pass-Through mode 0 = Inactive 1 = Active
<0>	Not used

6. Modulator Information

6.1 ISL9538C Buck-Boost Charger Modes of Operation

The ISL9538C buck-boost charger drives an external N-channel MOSFET bridge made of two transistor pairs as shown in [Figure 24](#). The first pair, Q1 and Q2, is a buck arrangement with the transistor center tap connected to an inductor “input” as is the case with a buck converter. The second transistor pair, Q3 and Q4, is a boost arrangement with the transistor center tap connected to the same “output” of the inductor as is the case with a boost converter. This arrangement supports bucking from a voltage input higher than the battery and also boosting from a voltage input lower than the battery.

Table 23. Operation Mode

Mode	Q1	Q2	Q3	Q4
Buck	Control FET	Sync. FET	OFF	ON
Boost	ON	OFF	Control FET	Sync. FET
Buck-Boost	Control FET	Sync. FET	Control FET	Sync. FET
Pass-Through	ON	OFF	OFF	ON

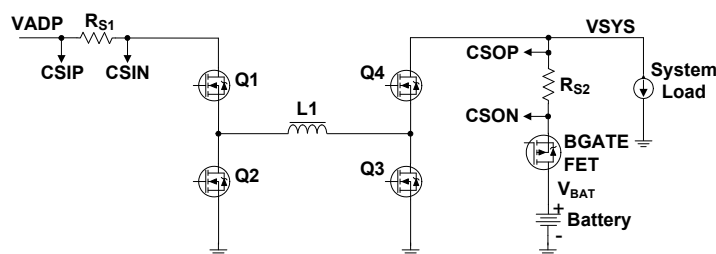


Figure 24. Buck-Boost Charger Topology

The ISL9538C optimizes the Operation mode transition algorithm by comparing the input and output voltage ratio and the load condition. When the adapter voltage V_{ADP} is rising and is higher than 94% of the system bus voltage V_{SYS} , the ISL9538C transitions from Boost mode to Buck-Boost mode. If V_{ADP} is higher than 112% of V_{SYS} , the ISL9538C forcedly transitions from Buck-Boost mode to Buck mode at any circumstance. At heavier loads, the mode transition point changes accordingly to accommodate the duty cycle change due to the power loss on the charger circuit.

When the adapter voltage V_{ADP} is falling and is lower than 106% the system bus voltage V_{SYS} , the ISL9538C transitions from Buck mode to Buck-Boost mode. If V_{ADP} is lower than 92% of V_{SYS} , the ISL9538C transitions from Buck-Boost mode to Boost mode.

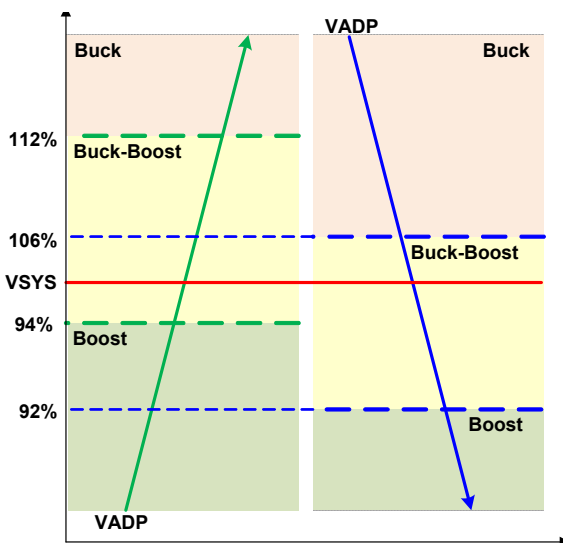


Figure 25. Operation Mode

The ISL9538C can be configured to operate in 2-FETs Buck mode as shown in [Figure 2](#). 2-FETs Buck mode can be entered when LGATE2 is connected to GND. When selecting 2-FETs Buck mode, configure the UGATE2, PHASE2, and BOOT2 pins as shown in [Figure 2](#). The controller operates in Buck mode only, disabling boost and buck-boost control loops.

After programming Force Buck Mode, the ISL9538C operates in Buck mode instead of Buck-Boost mode when VADP is 480mV higher than VSYS. Force Buck mode has a 240mV hysteresis window, so the ISL9538C operates in Buck-Boost mode when VADP is lower than VSYS + 240mV.

6.1.1 Pass-Through Mode

Enable Pass-Through mode with Control2 register Bit <0>. When the Pass-Through mode control bit is enabled, REF ramps to the input voltage and the switcher continues switching until the output voltage is in the 300mV window to the input. When the regulating voltage is within the 300mV window to the input voltage, the latch is set to stop switching. Q1 and Q4 are always on while Q2 and Q3 are always off. The ISL9538C enters Pass-Through mode and all protections are still valid. The following methods can be used to exit Pass-Through mode.

- Unprogram Control2 register Bit<0>. The REF ramps to the DAC and switching resumes
- Enable adapter OV triggers
- Ideal DE mode is enabled or the battery discharge current is higher than 300mA

Before entering Pass-Through mode, it is recommended to:

1. Ensure CV mode operation
2. Enable slew rate Ctrl6<6> = 1
3. Change Vsystmax DAC to the value as close to VADP as possible.

When Q1 and Q4 are latching on to enter Pass-Through mode, the current limit loop turns on for more than 1ms.

6.2 Modulator Control Loops

The four main control loops for the modulator are shown in [Figure 26](#). Each loop has a DAC register to provide settings as needed for each system.

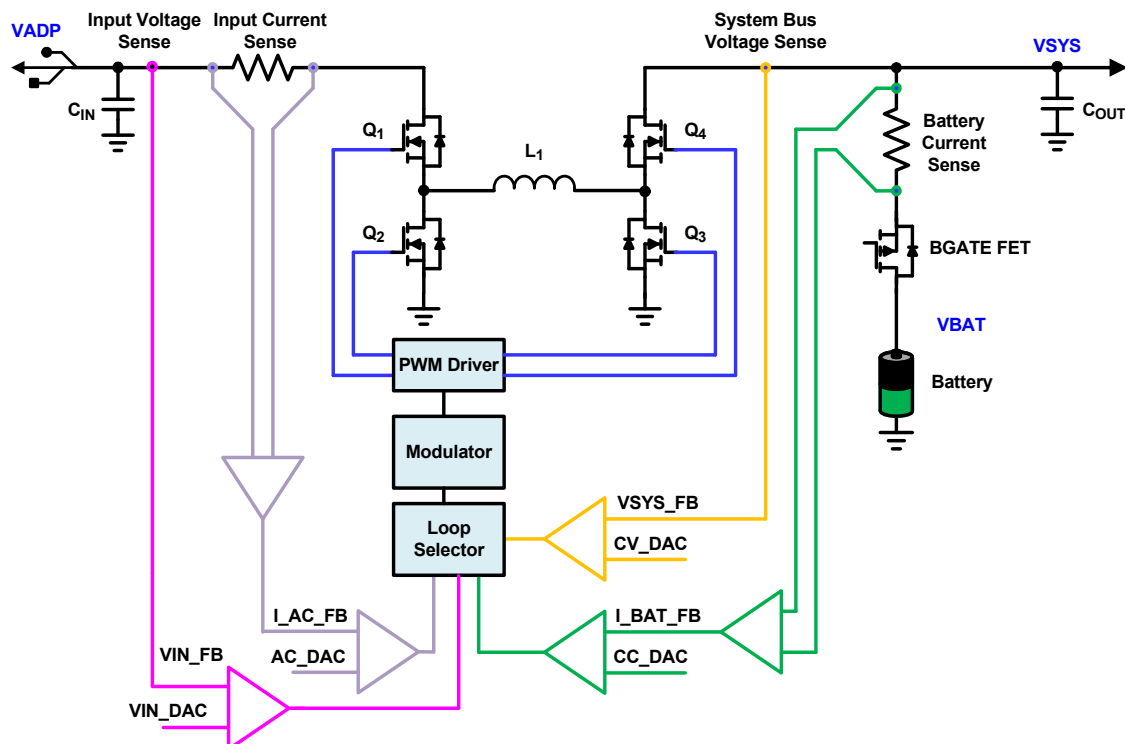


Figure 26. Charger Control Loops

6.2.1 Adapter Current Loop and Two-Level Current Limit

To set the adapter current limit, write a 16-bit AdapterCurrentLimit1 command to register address 0x3FH and/or an AdapterCurrentLimit2 command to register address 0x3BH using the Write-word protocol for a 20mΩ Rs1. See [Table 2](#) for the DAC summary of values.

The ISL9538C limits the adapter current by limiting the CSIP - CSIN voltage. By using the recommended current sense resistor values, the LSB of the register always translates to 4mA of adapter current. Any adapter current limit command is accepted; however, only the valid register bits are written to the AdapterCurrentLimit1 and AdapterCurrentLimit2 registers and the maximum value is clamped.

After adapter POR, the AdapterCurrentLimit1 register is reset to the value programmed through the PROG pin resistor. The AdapterCurrentLimit2 register is set to its default value of 1.5A or keeps the value that is written to it previously if the battery is present first. The AdapterCurrentLimit1 and AdapterCurrentLimit2 registers can be read back to verify their content. By default, the two level adapter current limit is disabled.

The AdapterCurrentLimit2 register has the same specification as the AdapterCurrentLimit1 register.

The two-level adapter current limit function can be enabled and disabled through SMBus Control2 register Bit<12> and the t1, t2 settings are configured by the Control5 register. When the two-level adapter current limit function is disabled, only the AdapterCurrentLimit1 value is used as the adapter current limit and AdapterCurrentLimit2 value is ignored.

In a real system, a Turbo event usually does not last very long. It is often no longer than milliseconds, a time length during which the adapter can supply current higher than its DC rating. The ISL9538C uses a two-level adapter current limit to fully take advantage of the surge capability of the adapter and minimize the power drawn from the battery.

[Figure 27](#) shows the two SMBus programmable adapter current limit levels, AdapterCurrentLimit1 and AdapterCurrentLimit2, as well as the durations t1 and t2. The two-level adapter current limit function is initiated when the adapter current is less than 100mA lower than the AdapterCurrentLimit1 register setting. It starts at AdapterCurrentLimit2 for duration t2, then changes to AdapterCurrentLimit1 for duration t1 before repeating the pattern. These parameters can set the adapter current limit with an envelope that allows the adapter to temporarily output surge current without requiring the charger to enter Turbo mode. This operation maximizes battery life.

The AdapterCurrentLimit1 register value can be higher or lower than the AdapterCurrentLimit2 value.

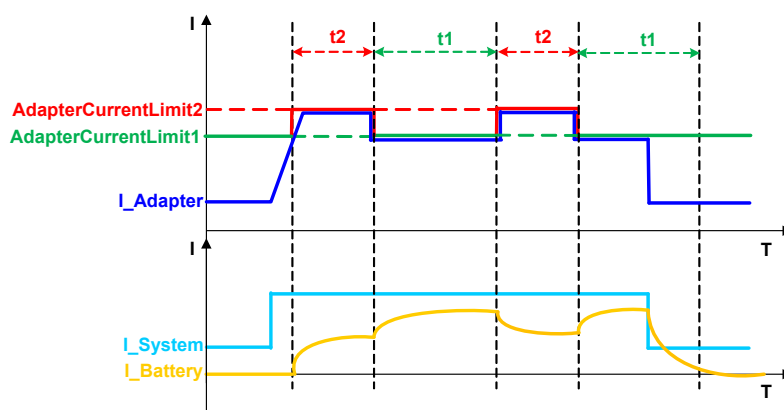


Figure 27. Two-Level Adapter Current Limit

6.2.2 Input Voltage Regulation Loop

6.2.2.1 Adapter Support Voltage

The input voltage regulation register DAC ([Table 2](#)) contains the SMBus readable and writable input voltage limit at which the input voltage loop tries to regulate when the input voltage is dropping. When the ADP is browning out or weak, the input voltage can droop. The input voltage loop tries to regulate to this setting by reducing battery charging current and then system power to try to hold up the input voltage. The system voltage may start to droop if the input power is not high enough to support the system.

This register accepts any current command but only the valid register bits are written to the register. The maximum value is clamped.

6.2.3 System Voltage Regulation and Trickle Charging

This loop works for two different voltage settings, MaxSystemVoltage and MinSystemVoltage.

If the battery is absent, or present but BGATE is turned off or not charging, the system voltage is regulated to the same setting as the DAC. To set the maximum charging voltage or the system regulating voltage, write a 16-bit MaxSystemVoltage command to register address 0x15H using the Write-word protocol shown in [Figure 23](#) and the data format shown in [Table 19](#).

The ISL9538C supports trickle charging to an overly discharged battery. It can activate the trickle charging function when the battery voltage is lower than MinSystemVoltage setting. The VBAT pin is the battery voltage sense point for Trickle Charge mode.

To enable Trickle Charging, set the ChargeCurrent register to a non-zero value. To disable trickle charging, set the ChargeCurrent register to 0. See [Table 24](#) for trickle charging control logic. The trickle charging current can be programmed to be 512mA, 256mA, 128mA, or 64mA through SMBus Control2 register Bit<15:14> as shown in [Table 14](#). In Trickle Charging mode, the ISL9538C regulates the trickle charging current through the buck-boost switcher. Another independent control loop controls the BGATE FET so that the system voltage is maintained at the voltage set in the MinSystemVoltage register. The VSYS pin is the system voltage sensing point in Trickle Charging mode.

When the battery voltage is charged to the MinSystemVoltage register value, the ISL9538C enters Fast Charging mode by limiting the charging current at the ChargeCurrentLimit register setting.

6.2.4 Charging Current Loop

This loop uses the charge current DAC (see [Table 3](#)) to set the fast charging current limit. To set it, write a 16-bit ChargeCurrentLimit command to register address 0x14H ([Table 2](#)).

The ISL9538C limits the charging current by limiting the CSOP - CSON voltage, so reducing the current sense resistor value doubles the current being regulated to. By using the recommended current sense resistor values $R_{s1} = 20\text{m}\Omega$ and $R_{s2} = 10\text{m}\Omega$, the LSB of the register always translates to 4mA of charging current. The ChargeCurrentLimit register accepts any charging current command, but only the valid register bits are written to the register.

6.2.5 Turbo Mode Support

Turbo mode refers the system drawing more power than the power rating of the adapter.

If the adapter current reaches the AdapterCurrentLimit1 register set value (or the AdapterCurrentLimit2 register set value, if the two-level adapter current limit function is enabled), or the adapter input voltage drops to the Input Voltage Regulation Reference set by Control0 register 0x39H Bit<2>, the ISL9538C limits the input power by regulating the adapter current at the AdapterCurrentLimit1/2 register set value, or by regulating the adapter voltage at the Input Voltage Regulation Reference point.

In Turbo mode, the system bus voltage VSYS drops automatically or the charging current drops automatically to limit the adapter input power. If the VSYS pin voltage is 150mV lower than the VBAT pin voltage, the BGATE FET turns on so that the battery supplies the rest of the power required by the system.

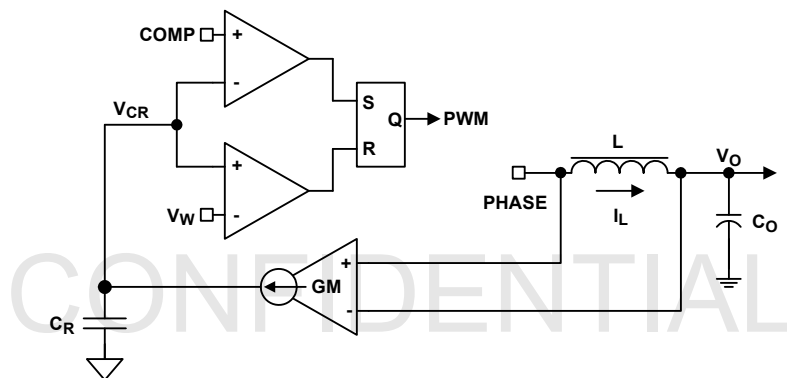
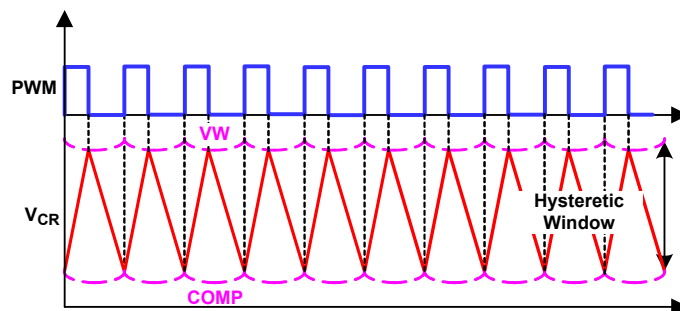
If the ISL9538C detects 150mA charging current or if the battery discharging current is less than 200mA for longer than 40ms or 80ms, it turns off BGATE to exit Turbo mode. The Turbo mode exit timer can be configured through Control3 register 0x4C Bit<8>. See [Table 24](#) for BGATE control logic.

Table 24. BGATE On/Off Truth Table

Turbo (Control Bit)	ChargeCurrent Register	BGATE On/Off	
		System Load Not In Turbo Mode Range	System Load in Turbo Mode Range
0	0	OFF	ON
0	1	ON for fast charge; Trickle charge is enabled	ON
1	0	OFF	OFF
1	1	ON for fast charge; Trickle charge is enabled	ON

6.3 R3 Modulator

The ISL9538C uses the Renesas Robust Ripple Regulator R3 modulation scheme. The R3 modulator combines the best features of fixed frequency PWM and hysteretic PWM while eliminating many of their shortcomings. [Figure 28](#) conceptually shows the R3 modulator circuit and [Figure 29](#) shows the operation principles in steady state.

**Figure 28. R3 Modulator****Figure 29. R3 Modulator Operation Principles In Steady State**

A fixed voltage window (VW window) exists between V_W and $COMP$. The modulator charges the ripple capacitor C_r with a current source equal to $g_m(V_{IN}-V_O)$ during PWM on-time and discharges the ripple capacitor C_r with a current source equal to $g_m V_O$ during PWM off-time, where g_m is a gain factor. The C_r voltage V_{CR} therefore emulates the inductor current waveform. The modulator turns off the PWM pulse when V_{cr} reaches V_W and turns on the PWM pulse when it reaches $COMP$.

Because the modulator works with V_{cr} , which is large amplitude and noise free synthesized signal, it achieves lower phase jitter than conventional hysteretic mode modulator.

[Figure 30](#) shows the operation principles during dynamic response. The COMP voltage rises during dynamic response, turning on PWM pulses earlier and more frequently temporarily, which allows for higher control loop bandwidth than conventional fixed frequency PWM modulators at the same steady state switching frequency.

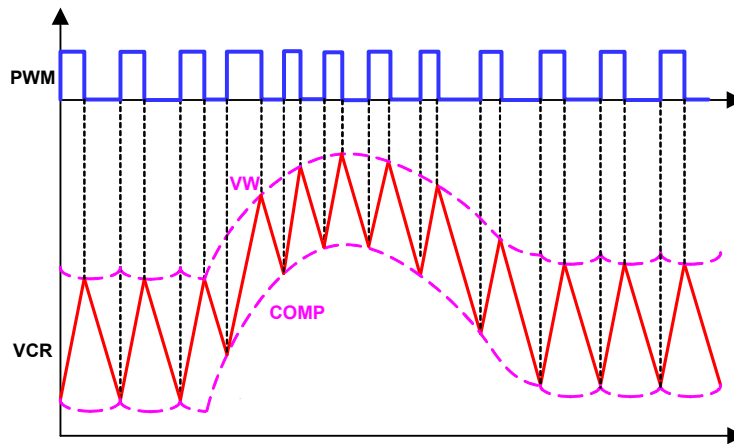


Figure 30. R3 Modulator Operation Principles In Dynamic Response

The R3 modulator can operate in Diode Emulation (DE) mode to increase light-load efficiency. In DE mode, the low-side MOSFET conducts when the current is flowing from source-to-drain and does not allow reverse current, which emulates a diode. As shown in [Figure 31](#), when LGATE is on, the low-side MOSFET carries current and creates negative voltage on the phase node due to the voltage drop across the ON-resistance. The IC monitors the current by monitoring the phase node voltage. It turns off LGATE when the phase node voltage reaches zero to prevent the inductor current from reversing the direction and creating unnecessary power loss.

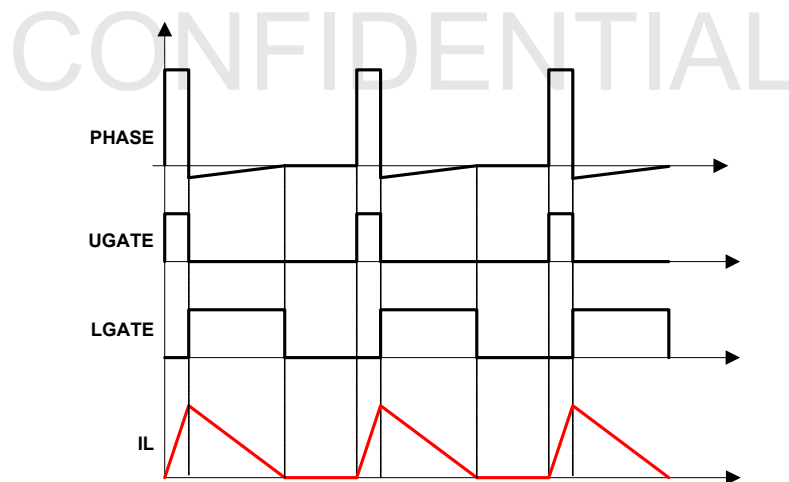


Figure 31. Diode Emulation

If the load current is light enough, as [Figure 31](#) shows, the inductor current reaches and stays at zero before the next phase node pulse, and the regulator is in Discontinuous Conduction Mode (DCM). If the load current is heavy enough, the inductor current never reaches 0A, and the regulator is in Continuous Conduction Mode (CCM) although the controller is in DE mode.

[Figure 32](#) shows the operation principle in DE mode at light load. The load gets incrementally lighter in the three cases from top to bottom. The PWM on-time is determined by the VW window size and therefore is the same, so the inductor current triangle is the same in the three cases. The R3 modulator clamps the ripple capacitor voltage V_{cr} in DE mode to mimic the inductor current. The COMP voltage takes longer to reach V_{cr} , which naturally stretches the switching period. The inductor current triangles move farther apart from each other so that the inductor current average value is equal to the load current. The reduced switching frequency helps increase light-load efficiency.

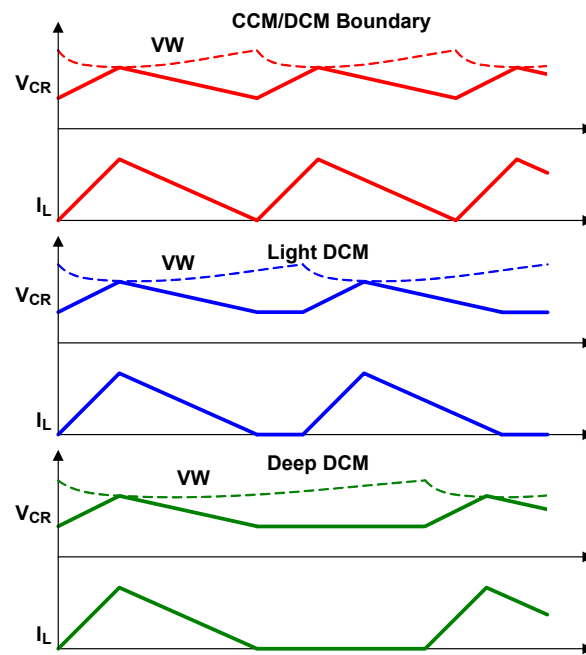


Figure 32. Period Stretching

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7. Application Information

7.1 Soft-Start

The ISL9538C includes a low power LDO with nominal 5V output, with an input OR-ed from the VBAT and ADP pins. The ISL9538C also includes a high power LDO with nominal 5V output, with an input from the DCIN pin that connects to both the adapter and the system bus through an external OR-ing diode circuit. Both LDO outputs are tied to the VDD pin to provide the bias power and gate drive power for the ISL9538C. The VDDP pin is the ISL9538C gate drive power supply input. Use an R-C filter to generate the VDDP pin voltage from the VDD pin voltage.

When $V_{DD} > 2.7V$, the ISL9538C digital block is activated and the SMBus register is ready to communicate with the master controller.

When $V_{ADP} > 3.2V$, after the 1.3s or 150ms debounce time set by Control2 register Bit<11> (the ASGATE turn-on delay is always 150ms the first time the adapter is plugged in after VDD POR), ASGATE starts turning on with 10 μ A of sink current. During the 1.3s or 150ms debounce time, the ISL9538C checks whether the input bus is short; if CSIP <2V or ACIN <0.8V, ASGATE does not turn on. The soft-start scheme carefully biases up the input capacitors and protects the back-to-back ASGATE FETs against potential damage caused by the inrush current.

Use a voltage divider from the adapter voltage to set the ACIN pin voltage. The ISL9538C monitors the ACIN pin voltage to determine the presence of the adapter. When $V_{DD} > 3.8V$, the ACIN pin voltage exceeds 0.8V, and ASGATE is fully turned on, the ISL9538C allows the external circuit to pull up the ACOK pin. When ACOK is asserted, the ISL9538C starts switching.

The ACOK is an open-drain output pin indicating the presence of the adapter and readiness of the adapter to supply power to the system bus. The ISL9538C actively pulls ACOK low in the absence of the adapter.

Before ASGATE turns ON, the ISL9538C sources 10 μ A of current out of the PROG pin and reads the pin voltage to determine the PROG resistor value. The PROG resistor programs the configurations of the ISL9538C.

In Battery Only mode, the ISL9538C enters Low Power mode if only the battery is present. V_{DD} is 5V from the low power LDO to minimize power consumption.

7.2 Programming Charger Option

The resistor from the PROG pin to GND programs the configuration of the ISL9538C for the default number of battery cells in series, the default switching frequency, the default AdapterCurrentLimit1 register value, and the autonomous charging function. The AdapterCurrentLimit2 register default value is 1.5A. [Table 25](#) shows the programming options.

Table 25. PROG Pin Programming Options

PROG-GND Resistance (k Ω)			Cell Number	Default Switching Frequency (Hz)	Autonomous Charging	Default ACLimit1 Reg (A)
Min	Typ 1%	Max				
42.7	43.2	43.7	2	733k	Yes	1.5
51.7	52.3	52.9		733k	Yes	0.476
61.2	61.9	62.6		1M	No	0.476
70.6	71.5	72.4		1M	No	1.5
81.5	82.5	83.5		733k	No	1.5
92.0	93.1	94.2		733k	No	0.476
104	105	106	3	733k	No	0.476
116	118	120		733k	No	1.5
131	133	135		1M	No	1.5
145	147	149		1M	No	0.476
160	162	164		733k	Yes	0.476
176	178	180		733k	Yes	1.5

Table 25. PROG Pin Programming Options (Continued)

PROG-GND Resistance (kΩ)			Cell Number	Default Switching Frequency (Hz)	Autonomous Charging	Default ACLimit1 Reg (A)
Min	Typ 1%	Max				
194	196	198	4	733kHz	Yes	1.5
212	215	218		733kHz	Yes	0.476
234	237	240		1MHz	No	0.476
258	261	264		1MHz	No	1.5
284	287	290		733kHz	No	1.5
312	316	320		733kHz	No	0.476

The ISL9538C uses the default number of cells in series as [Table 25](#) shows and sets the default MaxSystemVoltage register value and default MinSystemVoltage register value accordingly.

The switching frequency can be changed through SMBus Control1 register Bit<9:8> after POR. See the SMBus Control1 register programming table ([Table 13](#)) for a detailed description.

Before ASGATE turns on, the ISL9538C sources 10μA of current out of the PROG pin and reads the PROG pin voltage to determine the resistor value. However, application environmental noise can pollute the PROG pin voltage and cause incorrect readings. If noise is a concern, connect a capacitor from the PROG pin to GND to provide filtering. The resistor and the capacitor RC time constant should be less than 40μs so the PROG pin voltage can rise to steady state before the ISL9538C reads it.

If the ISL9538C is powered up from the battery, it does not read the PROG resistor unless PSYS is enabled through SMBus Control1 register Bit<3>. Whenever PSYS is enabled in Battery Only mode, the ISL9538C reads the PROG pin resistor and resets the configuration to the default. When the adapter is plugged in, the ISL9538C resets the AdapterCurrentLimit1 register to the default by reading the PROG pin resistor if it was not read before, or by loading the previous readings.

If PSYS is not enabled, the ISL9538C resets the MaxSystemVoltage register and MinSystemVoltage register to their default values according to the PROG pin cell number setting. If PSYS is enabled, the ISL9538C keeps the values in these two registers.

By default, the adapter current sensing resistor R_{S1} is 20mΩ and the battery current sensing resistor R_{S2} is 10mΩ. Using this $R_{S1} = 20\text{m}\Omega$ and $R_{S2} = 10\text{m}\Omega$ option results in a 4mA/LSB correlation in the SMBus current commands.

If the R_{S1} and R_{S2} values are different from this $R_{S1} = 20\text{m}\Omega$ and $R_{S2} = 10\text{m}\Omega$ option, the SMBus command needs to be scaled accordingly to obtain the correct current. Smaller current sense resistor values reduce power loss while larger current sense resistor values give better accuracy.

If different current sensing resistors are used, the $R_{S1}:R_{S2}$ ratio should be kept as 2:1, and the PSYS output can be scaled accordingly to reflect the total system power correctly. The information in this datasheet is based on current sensing resistors $R_{S1} = 20\text{m}\Omega$ and $R_{S2} = 10\text{m}\Omega$ unless specified otherwise.

7.3 Autonomous Charging Mode

Autonomous Charging mode can be enabled or disabled through the programming charging option resistor or SMBus Control3 register Bit<7>. When Autonomous Charging mode is enabled, this mode can also be disabled by writing to the SMBus ChargingCurrentLimit or MaxSystemVoltage command.

The ISL9538C enters Autonomous Charging mode when the battery voltage is lower than MaxSystemVoltage - 200mV per cell for 1ms of debounce time and the BGATE MOSFET is on.

In Autonomous Charging mode, the ISL9538C starts to charge the battery with 2A (with $R_{S2} = 10\text{m}\Omega$), the PROCHOT# pin (Autonomous Charging mode indication pin) is pulled down to GND, and the 175s charging timeout timer is disabled. The ISL9538C exits from Autonomous Charging mode when the battery charging current is less than 200mA (with $R_{S2} = 10\text{m}\Omega$) for 20ms or 200ms in CV loop. This autonomous charging termination time can be set by Control3 register Bit<13>. The ISL9538C re-enters Autonomous Charging mode when the battery voltage is discharged below MaxSystemVoltage - 200mV per cell. When the ISL9538C stays in Autonomous Charging mode for 12hrs, which means the battery charging current is higher than 200mA and the battery cannot be charged to MaxSystemVoltage for 12hrs, the ISL9538C stops charging the battery and exits Autonomous Charging mode.

7.4 Battery Ship Mode

The ISL9238C supports Battery Ship mode. When Control3 register Bit <10> is 1, the BGATE MOSFET stays off for Battery Ship mode.

Battery Ship mode sets the lowest power state for the IC. Ship mode can only be entered from Battery Only mode. To achieve the lowest power, several analog functions must be disabled. Many are disabled by default and do not need to be written, but all are listed for completeness. However, the power level can be customized for the system.

- Control1 0x3Ch
 - Bit<5> = 1 Disable IMON
 - Bit<3> = 0 Disable PSYS
- Control2 0x3Dh
 - Bit<3> = 1 Disable GP Comparator
- Control3 0x4Ch
 - Bit<10> = 1 Force BGATE Off

To exit Battery Ship mode, use the SMBus to change the control bits.

7.5 Diode Emulation Operation

In Diode Emulation (DE) mode, the ISL9538C uses a phase comparator to monitor the PHASE node voltage during the low-side switching FET on-time to detect the inductor current zero crossing. The phase comparator needs a minimum on-time of the low-side switching FET to recognize inductor current zero crossing. If the low-side switching FET on-time is too short for the phase comparator to successfully recognize the inductor zero crossing, the ISL9538C can lose DE ability. To prevent this, the ISL9538C uses a minimum low-side switching FET on-time. When the intended low-side switching FET on-time is shorter than the minimum value, the ISL9538C stretches the switching period to keep the low-side switching FET on-time at the minimum value, which causes the CCM switching frequency to drop below the set point.

7.6 Battery Learn Mode

Use Battery Learn mode to supply the system power from the battery even when the adapter is plugged in, such as calibration of the battery fuel gauge.

The ISL9538C enters Battery Learn mode when it receives the SMBus Control command. When entering Battery Learn mode, the ISL9538C turns on the BGATE FET.

In Battery Learn mode, the ISL9538C turns on BGATE and keeps ASGATE on but turns off the buck-boost switcher regardless of whether the adapter is present.

The three ways of exiting Battery Learn mode are:

- Receive the Battery Learn mode exit command through SMBus
- The battery voltage is less than MinSystemVoltage register setting (according to the Control1 register Bit<12> setting)
- The BATGONE pin voltage goes from logic LOW to HIGH

In all these cases, the ISL9538C resumes switching immediately to supply power to the system bus from the adapter to prevent system voltage collapse.

7.7 Charger Timeout

The ISL9538C includes a timer to ensure the SMBus master is active and to prevent overcharging the battery. The ISL9538C terminates charging by turning off the BGATE FET if the charger has not received a write command to the MaxSystemVoltage or ChargeCurrent register within 175s (SMBus Control3 register Bit<12:11> = 00). Charger timeout time can be configured through SMBus Control3 register Bit<12:11>. When charging is terminated by the timeout, the ChargeCurrent register retains its value instead of resetting to zero. If a timeout occurs, the MaxSystemVoltage or ChargeCurrent register must be written to re-enable charging.

The ISL9538C allows you to disable the charger timeout function through SMBus Control0 register Bit<7> as [Table 12](#) shows.

7.8 Monitoring

7.8.1 Current Monitor

The ISL9538C provides an adapter current monitor or a battery charging current monitor/battery discharging current monitor through the AMON/BMON pin. The AMON output voltage is $18x (CSIP - CSIN)$ and $18x (CSIN - CSIP)$ voltage. The BMON output voltage is $18x (CSON - CSOP)$ and $36x (CSOP - CSON)$ voltage.

The AMON and BMON functions can be enabled or disabled through SMBus Control1 register Bit<5>. AMON or BMON can be selected through SMBus Control1 register Bit<4> and the AMON/BMON direction can be configured through SMBus Control3 register Bit<3> as [Table 13](#) shows.

7.8.2 PSYS Monitor

The ISL9538C PSYS pin provides a measure of the instantaneous power consumption of the entire platform. The PSYS pin outputs a current source described by [Equation 1](#).

$$(EQ. 1) \quad I_{PSYS} = K_{PSYS} \times (V_{ADP} \times I_{ADP} + V_{BAT} \times I_{BAT})$$

K_{PSYS} is based on the current sensing resistor $R_{s1} = 20m\Omega$ and $R_{s2} = 10m\Omega$. V_{ADP} is the adapter voltage in V, I_{ADP} is the adapter current in A, V_{BAT} is the battery voltage, and I_{BAT} is the battery discharging current. When the battery is discharging, I_{BAT} is a positive value; when the battery is being charged, I_{BAT} is a negative value. The battery voltage V_{BAT} is detected through the CSON pin to maximize the power monitor accuracy in NVDC configuration Trickle Charge mode.

The R_{s1} to R_{s2} ratio must be 2:1 for valid power calculation. If the resistance values are higher (or lower) than the suggested values mentioned previously, K_{PSYS} is proportionally higher (or lower). As an example, if $R_{s1} = 10m\Omega$ and $R_{s2} = 5m\Omega$, the output current is half that above for the same power. If the PSYS information is not needed, any $R_{s1}:R_{s2}$ ratio is acceptable.

The PSYS gain can be configured through SMBus Control3 register Bit<9>. The default PSYS gain is set to $1.467\mu A/W$ and a $0.734\mu A/W$ PSYS gain option is available.

The PSYS information includes the power loss of the charger circuit and the actual power delivered to the system. The resistor R_{PSYS} connected between the PSYS pin and GND converts the PSYS information from current to voltage.

PSYS accuracy limits and a typical accuracy scan are shown in [Figure 33](#).

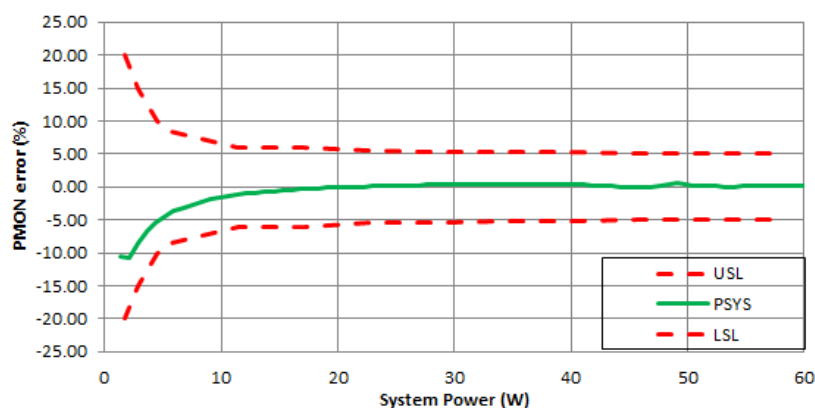


Figure 33. PSYS Accuracy and Limits

The PSYS function can be enabled or disabled through SMBus Control1 register Bit<3> as shown in [Table 13](#).

In Battery Only mode, the PSYS function cannot work if the battery voltage is less than 5.2V.

7.9 Stand-Alone Comparator

The ISL9538C includes a general purpose stand-alone comparator. The CMIN pin is the comparator input. The internal comparator reference is connected to the inverting input of the comparator and can be configured as 1.2V or 2V through SMBus Control2 register Bit<4>. The comparator output is the CMOUT pin. The output polarity can be configured through the SMBus register bit when the comparator is tripped.

- When Control2 register Bit<2> = 0 for normal comparator output polarity, CMOUT = High if CMIN > Reference; CMOUT = Low if CMIN < Reference.
- When Control2 register Bit<2> = 1 for inversed comparator output polarity, CMOUT = Low if CMIN > Reference; CMOUT = High if CMIN < Reference.

By default in Battery Only mode, the stand-alone comparator is enabled. This comparator can be enabled/disabled in Battery Only mode using Control 2 Bit <3>. In Battery Only mode, the reference is set to 1.2V only.

[Table 26](#) shows the stand-alone comparator truth table.

Table 26. Comparator Truth Table

	Description
Control2 Bit<3> Comparator Enable/Disable	0 = The comparator is enabled 1 = The comparator is disabled

7.10 Protections

7.10.1 Adapter Overvoltage Protection

If the ADP pin voltage exceeds 23.4V for more than 10μs, an adapter overvoltage condition occurs. The ISL9538C turns off the ASGATE MOSFETs to isolate the adapter from the system, deasserts the ACOK signal by pulling it low, and stops switching. BGATE turns on for the battery to support the system load. When the ADP voltage drops below 23.04V from more than 100μs, it starts to turn on ASGATE and starts switching.

7.10.2 System Overvoltage Protection

The ISL9538C provides system rail overvoltage protection. If the system voltage VSYS is 800mV higher than MaxSystemVoltage register set value, it declares the system overvoltage and stops switching. It resumes switching without the 1.3s or 150ms debounce when VSYS drops 400mV below the system overvoltage threshold.

7.10.3 System Voltage Rail Short Protection

The ISL9538C has a system rail short protection (VSYSOK) to prevent powering on the system rail into a short-circuit before switching starts. When the VSYS voltage is below 0.6V, the ISL9538C sources 10mA current from VDDP to charge VSYS before switching can start.

From VSYSOK (VSYS rail short protection) beginning to switching start in VSYS state, the parts must go through multiple startup and initialization transition states, including turning on A-FET. This initialization transition duration may or may not take longer than VSYS voltage is charged above 0.6V using a 10mA source by the VSYSOK function. If this initialization transition duration is longer than the duration of charging VSYS above 0.6V, the charger must wait until the transition duration is completed before switching starts, and vice versa.

Conversely, the duration of charging VSYS above 0.6V, which depends on the leakage current and capacitance value at VSYS, varies per individual system design. If users would like to estimate the duration in a worst-case scenario, Renesas recommends testing their design to determine the following:

- If the initialization transition duration is longer than the duration of charging VSYS above 0.6V, one may add a 30% margin (considering ±5% clock tolerance) to estimate the duration.
- If the initialization transition duration is shorter than the duration of charging VSYS above 0.6V, one can check the tolerance of the VSYS capacitance or leakage current from VSYS downstream circuitry and then add a reasonable margin, such as 40% (considering ±20% cap tolerance), to estimate the duration.

After switching starts, the charger enters the Fault state if VSYS drops below 0.6V again at any time. After entering the Fault state, the charger stops switching and turns off ASGATE, and tries to start again with 1.3s or 150ms debounce time (configured by control2<11>).

For ISL9538C startup without battery pack present, Renesas recommends checking total system loading on VSYS, zero load preferred, and ensure it does not exceed the worse-case value, VSYS loading <19.8μA for VSYS <0.6V.

7.10.4 System Voltage Undervoltage Protection (for Short-Circuit Protection)

The charger has a fixed undervoltage protection on the system side that can be configured using Control 6<2:0>.

When inserting the battery for the first time, VSYS UV by default is 000 = Disabled. When inserting the adapter, VSYS UV threshold by default is 011 = 4.8V. When the VSYS voltage falls to the VSYS UV threshold set by Control 6<2:0>, there is a 100ms debounce before the charger enters FAULT state. After entering FAULT state, there is no switching and charger tries to start switching again after 1.3s (configurable by Control 2<11>).

7.10.5 Over-Temperature Protection

The ISL9538C stops switching for self protection when the junction temperature exceeds +140°C. When the temperature falls below +120°C and after a 100μs delay, the ISL9538C resumes switching.

7.11 Selecting the Power Source

The ISL9538C automatically selects the adapter and/or the battery as the source for system power.

The BGATE pin drives a P-channel MOSFET gate that connects/disconnects the battery from the system and the switcher.

The ASGATE pin drives a pair of back-to-back common source PFETs to connect/disconnect the adapter from the system and the battery. Use of the ASGATE pin is optional.

When the battery voltage V_{BAT} is higher than 2.4V and the adapter voltage V_{ADP} is less than 3.2V, the ISL9538C operates in Battery Only mode. During Battery Only mode, the ISL9538C turns on the BGATE FET to connect the battery to the system. In Battery Only mode, the ISL9538C consumes very low power (less than 20μA). The battery discharging current monitor BMON can be turned on during this mode to monitor the battery discharging current. If the battery voltage V_{BAT} is higher than 5.2V, the system power monitor PSYS function also can be turned on during this mode to monitor system power.

When the adapter voltage V_{ADP} is more than 3.2V, the ISL9538C turns on ASGATE. If VDD is higher than 3.8V, the ISL9538C enters Forward Buck, Forward Boost, or Forward Buck-Boost mode depending upon the adapter and system voltage VSYS duty cycle ratio. The system bus voltage is regulated at the voltage set on the MaxSystemVoltage register. If the charge current register is programmed (non-zero), the ISL9538C charges the battery either in Trickle Charging mode or Fast Charging mode, as long as BATGONE is low.

8. General Application Information

This design guide provides a high-level explanation of the steps necessary to design a single-phase power converter. It is assumed that the reader is familiar with many of the basic skills and techniques referenced in the following section. In addition to this guide, Renesas provides complete reference designs that include schematics, bill of materials, and example board layouts.

8.1 Selecting the LC Output Filter

The duty cycle of an ideal buck converter in CCM is a function of the input and the output voltage. This relationship is written by [Equation 2](#):

$$(EQ. 2) \quad D = \frac{V_{OUT}}{V_{IN}}$$

The output inductor peak-to-peak ripple current is written by [Equation 3](#):

$$(EQ. 3) \quad I_{P-P} = \frac{V_{OUT} \cdot (1 - D)}{f_{SW} \cdot L}$$

A typical step-down DC/DC converter has an I_{P-P} of 20% to 40% of the maximum DC output load current for a practical design. The value of I_{P-P} is selected based upon several criteria such as MOSFET switching loss, inductor core loss, and the resistive loss of the inductor winding.

The DC copper loss of the inductor can be estimated by [Equation 4](#):

$$(EQ. 4) \quad P_{COPPER} = I_{LOAD}^2 \cdot DCR$$

where I_{LOAD} is the converter output DC current.

The copper loss can be significant, so select DCR carefully. Another factor to consider when choosing the inductor is its saturation characteristics at elevated temperatures. A saturated inductor can destroy circuit components.

A DC/DC buck regulator must have output capacitance C_O into which ripple current I_{P-P} can flow. Current I_{P-P} develops a corresponding ripple voltage V_{P-P} across C_O , which is the sum of the voltage drop across the capacitor ESR and of the voltage change stemming from charge moved in and out of the capacitor. These two voltages are written by [Equation 5](#) and [Equation 6](#):

$$(EQ. 5) \quad \Delta V_{ESR} = I_{P-P} \cdot ESR$$

$$(EQ. 6) \quad \Delta V_C = \frac{I_{P-P}}{8 \cdot C_O \cdot f_{SW}}$$

If the output of the converter has to support a load with high pulsating current, several capacitors need to be paralleled to reduce the total ESR until the required V_{P-P} is achieved. The inductance of the capacitor can cause a brief voltage dip if the load transient has an extremely high slew rate. Low inductance capacitors should be considered in this scenario. A capacitor dissipates heat as a function of RMS current and frequency. Ensure that I_{P-P} is shared by a sufficient quantity of paralleled capacitors so that they operate below the maximum rated RMS current at f_{SW} . Take into account that the rated value of a capacitor can fade as much as 50% as the DC voltage across it increases.

8.2 Selecting the Input Capacitor

The important parameters for input capacitance are the voltage rating and the RMS current rating. For reliable operation, select capacitors with voltage and current ratings above the maximum input voltage and that are capable of supplying the RMS current required by the switching circuit. Their voltage rating should be at least 1.25x greater than the maximum input voltage, while a voltage rating of 1.5x is a preferred rating. [Figure 34](#) is a graph of the input capacitor RMS ripple current that is normalized relative to output load current. The graph is also a function of duty cycle and is adjusted for converter efficiency.

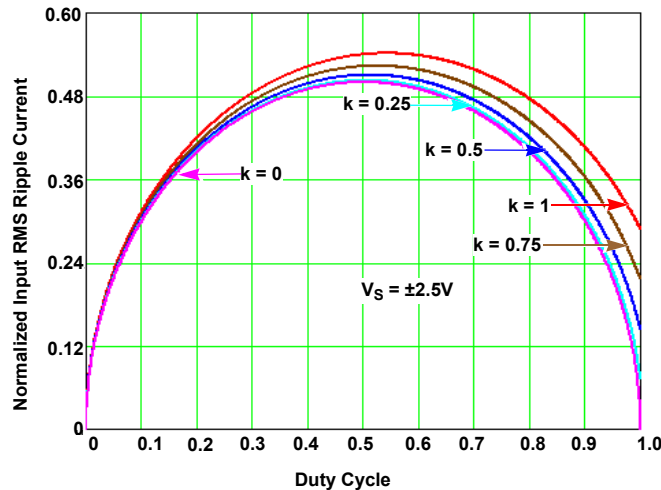


Figure 34. Normalized RMS Input Current at EFF = 1

The normalized RMS ripple current calculation is written by [Equation 7](#):

$$(EQ. 7) \quad I_{C_{IN}(RMS,NORMALIZED)} = \frac{I_{MAX} \cdot \sqrt{D \cdot (1-D) + \frac{D \cdot k^2}{12}}}{I_{MAX}}$$

where:

- I_{MAX} is the maximum continuous I_{LOAD} of the converter
- k is a multiplier (0 to 1) corresponding to the inductor peak-to-peak ripple amplitude expressed as a ratio of I_{MAX} (0 to 1)
- D is the duty cycle that is adjusted to take into account the efficiency of the converter, which is written by [Equation 8](#):

$$(EQ. 8) \quad D = \frac{V_{OUT}}{V_{IN} \cdot EFF}$$

In addition to the capacitance, some low ESL ceramic capacitance is recommended to decouple between the drain of the high-side MOSFET and the source of the low-side MOSFET.

8.3 Selecting the Switching Power MOSFET

Typically, a MOSFET cannot tolerate even brief excursions beyond its maximum drain-to-source voltage rating. The MOSFETs used in the power stage of the converter should have a maximum V_{DS} rating that exceeds both the sum of the upper voltage tolerance of the input power source and the voltage spike that occurs when the MOSFET switches off.

Several power MOSFETs that are optimized for DC/DC converter applications are readily available. The preferred high-side MOSFET emphasizes low gate charge so that the device spends the least amount of time dissipating power in the linear region. Unlike the low-side MOSFET, which has the drain-to-source voltage clamped by its body diode during turn off, the high-side MOSFET turns off with a V_{DS} of approximately $V_{IN} - V_{OUT}$, plus the spike across it. The preferred low-side MOSFET emphasizes low $r_{DS(ON)}$ when fully saturated to minimize conduction loss.

Note: This is an optimal configuration of MOSFET selection for low duty cycle applications ($D < 50\%$). For higher output, low input voltage solutions, a more balanced MOSFET selection for high-side and low-side devices may be needed.

The Low-Side (LS) power loss of the [MOSFET can be assumed to be conductive only and is written as [Equation 9](#):

$$(EQ. 9) \quad P_{CON_LS} = I_{LOAD}^2 \cdot r_{DS(ON)_LS} \cdot (1 - D)$$

The conduction loss of the High-Side (HS) MOSFET is written by [Equation 10](#):

$$(EQ. 10) \quad P_{CON_HS} = I_{LOAD}^2 \cdot r_{DS(ON)_HS} \cdot D$$

The switching loss of the HS MOSFET is written by [Equation 11](#):

$$(EQ. 11) \quad P_{SW_HS} = \frac{V_{IN} \cdot I_{VALLEY} \cdot t_{SW(ON)} \cdot f_{SW}}{2} + \frac{V_{IN} \cdot I_{PEAK} \cdot t_{SW(OFF)} \cdot f_{SW}}{2}$$

where:

- I_{VALLEY} is the difference of the DC component of the inductor current minus 1/2 of the inductor ripple current
- I_{PEAK} is the sum of the DC component of the inductor current plus 1/2 of the inductor ripple current
- $t_{SW(ON)}$ is the time required to drive the device into saturation
- $t_{SW(OFF)}$ is the time required to drive the device into cut-off

8.4 Selecting the Bootstrap Capacitor

The selection of the bootstrap capacitor is written by [Equation 12](#):

$$(EQ. 12) \quad C_{BOOT} = \frac{Q_g}{\Delta V_{BOOT}}$$

where:

- Q_g is the total gate charge required to turn on the high-side MOSFET
- ΔV_{BOOT} is the maximum allowed voltage decay across the boot capacitor each time the high-side MOSFET is switched on.

As an example, suppose the HS MOSFET has a total gate charge Q_g of 25nC at $V_{GS} = 5V$ and a ΔV_{BOOT} of 200mV. The calculated bootstrap capacitance is 0.125μF; for a comfortable margin, select a capacitor that is double the calculated capacitance. In this example, 0.22μF is sufficient. Use an X7R or X5R ceramic capacitor. Renesas recommends using a 0.47μF (25V) bootstrap capacitor, which has an effective capacitance higher than 0.25μF at 5V and x50 effective high side MOSFET gate capacitance.

8.5 Switching Power MOSFET Gate Capacitance

The ISL9538C includes an internal 5V LDO output at the VDD pin that can provide the switching MOSFET gate driver power through the VDDP pin with an R-C filter. The 5V LDO output overcurrent protection threshold is 100mA nominal. When selecting the switching power MOSFET, consider the MOSFET gate capacitance carefully to avoid overloading the 5V LDO, especially in Buck-Boost mode when four MOSFETs are switching at the same time. For one MOSFET, the gate drive current can be estimated by [Equation 13](#):

$$(EQ. 13) \quad I_{driver} = Q_g \cdot f_{SW}$$

where:

- Q_g is the total gate charge, which can be found in the MOSFET datasheet
- f_{SW} is the switching frequency

Renesas recommends using a 2.2μF (10V) VDD/VDDP capacitor, which has an effective capacitance higher than 0.4μF at 5V and x1.6 effective cap at the BOOT pin at 5V.

8.6 DCIN Filter

An RC filter is connected at the DCIN pin. Renesas recommends connecting a 10Ω DCIN resistor between the DCIN pin and the VADP/VSYS diodes, and connecting a 4.7μF DCIN capacitor to GND, which has an effective capacitance higher than 0.4μF at 20V.

8.7 Adapter Input Filter

The adapter cable parasitic inductance and capacitance can cause some voltage ringing or an overshoot spike at the adapter connector node when the adapter is hot plugged in. This voltage spike can damage the ASGATE MOSFET or the ISL9538C pins connecting to the adapter connector node. One low cost solution is to add an R-C snubber circuit at the adapter connector node to clamp the voltage spike as shown in [Figure 35](#). A practical value of the R-C snubber is 2.2Ω to 2.2μF, while the appropriate values and power rating should be carefully characterized based on the actual design. Renesas does not recommend adding a pure capacitor at the adapter connector node, which can cause an even larger voltage spike due to the adapter cable or the adapter current path parasitic inductance.

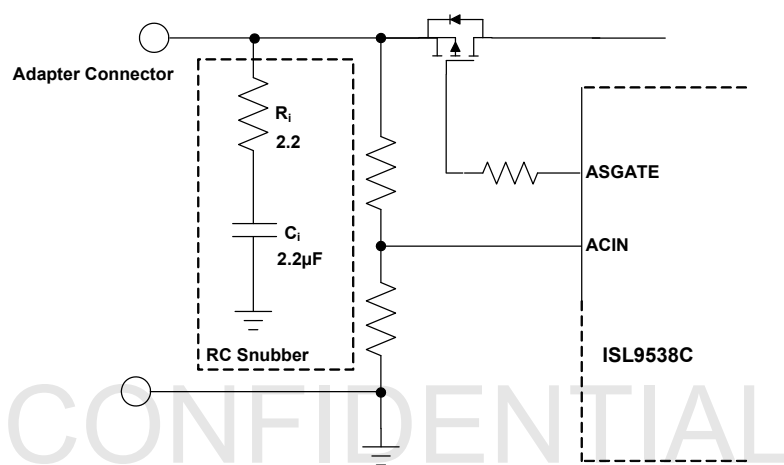
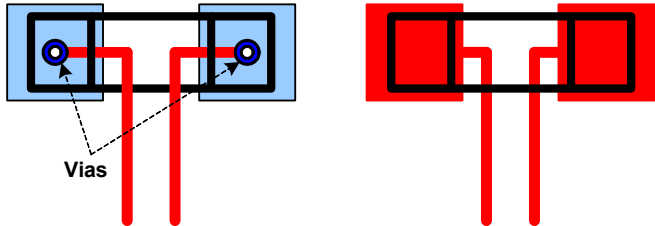
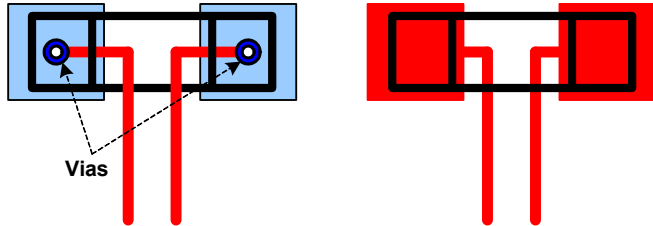


Figure 35. Adapter Input RC Snubber Circuit

9. Layout

Pin Number	Pin Name	Layout Guidelines
Bottom Pad 33	GND	Connect this ground pad to the ground plane through a low impedance path. Use at least five vias to connect to the PCB ground planes to ensure sufficient thermal dissipation directly under the IC.
1	CSON	Run two dedicated traces with sufficient width in parallel (close to each other to minimize the loop area) from the two terminals of the battery current sensing resistor to the IC. Place the differential mode and common-mode RC filter components in the general proximity of the controller. Route the current sensing traces through vias to connect the center of the pads; or route the traces into the pads from the inside of the current sensing resistor. The following drawings show the two preferred ways of routing current sensing traces.  Current Sensing Traces Current Sensing Traces
2	CSOP	
3	VSYS	This signal pin provides feedback for the system bus voltage. Place the optional R-C filter in the general proximity of the controller. Run a dedicated trace from the system bus to the pin and do not route near the switching traces. Do not share the same trace with the signal routing to the DCIN pin OR diodes and the CSOP trace.
4	BOOT2	Switching pin. Place the bootstrap capacitor in the general proximity of the controller. Use sufficiently wide traces. Avoid any sensitive analog signal traces from crossing over or getting close.
5	UGATE2	Run these two traces in parallel fashion with sufficient width. Avoid any sensitive analog signal traces from crossing over or getting close. Route the PHASE2 trace to the high-side MOSFET source pin instead of general copper. Place the IC close to the switching MOSFETs gate terminals and keep the gate drive signal traces short for a clean MOSFET drive. The IC can be placed on the opposite side of the switching MOSFETs. Place the output capacitors as close as possible to the switching high-side MOSFET drain and the low-side MOSFET source, and use shortest PCB trace connection. Place these capacitors on the same PCB layer with the MOSFETs instead of on different layers and using vias to make the connection. Place the inductor terminal to the switching high-side MOSFET source and low-side MOSFET drain terminal as close as possible. Minimize this phase node area to lower the electrical and magnetic field radiation but make this phase node area large enough to carry the current. Place the inductor and the switching MOSFETs on the same layer of the PCB.
6	PHASE2	
7	LGATE2	Switching pin. Run the LGATE2 trace in parallel with the UGATE2 and PHASE2 traces on the same PCB layer. Use sufficient width. Avoid any sensitive analog signal traces from crossing over or getting close.
8	VDDP	Place the decoupling capacitor in the general proximity of the controller. Run the trace connecting to the VDD pin with sufficient width.
9	LGATE1	Switching pin. Run the LGATE1 trace in parallel with the UGATE1 and PHASE1 traces on the same PCB layer. Use sufficient width. Avoid any sensitive analog signal traces from crossing over or getting close.
10	PHASE1	Run these two traces in parallel fashion with sufficient width. Avoid any sensitive analog signal traces from crossing over or getting close. Route the PHASE1 trace to the high-side MOSFET source pin instead of general copper. Place the IC close to the switching MOSFETs gate terminals and keep the gate drive signal traces short for a clean MOSFET drive. The IC can be placed on the opposite side of the switching MOSFETs. Place the input capacitors as close as possible to the switching high-side MOSFET drain and the low-side MOSFET source, and use shortest PCB trace connection. Place these capacitors on the same PCB layer with the MOSFETs instead of on different layers and using vias to make the connection. Place the inductor terminal to the switching high-side MOSFET source and low-side MOSFET drain terminal as close as possible. Minimize this phase node area to lower the electrical and magnetic field radiation but make this phase node area big enough to carry the current. Place the inductor and the switching MOSFETs on the same layer of the PCB.
11	UGATE1	

Pin Number	Pin Name	Layout Guidelines
12	BOOT1	Switching pin. Place the bootstrap capacitor in the general proximity of the controller. Use sufficient wide trace. Avoid any sensitive analog signal traces from crossing over or getting close.
13	ASGATE	Run this trace with sufficient width in parallel fashion with the ADP pin trace.
14	CSIN	Run two dedicated traces with sufficient width in parallel (close to each other to minimize the loop area) from the two terminals of the adapter current sensing resistor to the IC. Place the Differential mode and common-mode RC filter components in the general proximity of the controller. Route the current sensing traces through vias to connect the center of the pads or route the traces into the pads from the inside of the current sensing resistor. The following drawings show the two preferred ways of routing current sensing traces.  Current Sensing Traces Current Sensing Traces
15	CSIP	
16	ADP	Run this trace with sufficient width in parallel fashion with the ASGATE pin trace.
17	DCIN	Place the OR diodes and the RC filter in the general proximity of the controller. Run the VADP trace and VSYS trace to the OR diodes with sufficient width.
18	VDD	Place the RC filter connecting with the VDDP pin in the general proximity of the controller. Run the trace connecting to the VDDP pin with sufficient width.
19	ACIN	Place the voltage divider resistors and the optional decoupling capacitor in the general proximity of the controller.
20	CMIN	No special consideration.
21	SDA	Digital pins. No special consideration. Run the SDA and SCL traces in parallel.
22	SCL	
23	PROCHOT#	Digital pin, open-drain output. No special consideration.
24	ACOK	
25	BATGONE	Digital pin. Place the 100kΩ resistor series in the BATGONE signal trace and the optional decoupling capacitor in the general proximity of the controller.
26	CMOUT	Digital pin, open-drain output. No special consideration.
27	PROG	Signal pin. Place the PROG programming resistor in the general proximity of the controller.
28	COMP	Place the compensation components in the general proximity of the controller. Avoid any switching signal from crossing over or getting close.
29	AMON/BMON	No special consideration. Place the optional RC filter in the general proximity of the controller.
30	PSYS	Signal pin, current source output. No special consideration.
31	VBAT	Place the optional RC filter in the general proximity of the controller. Run a dedicated trace from the battery positive connection point to the IC.
32	BGATE	Use sufficient width trace from the IC to the BGATE MOSFET gate. Place the capacitor from BGATE to ground close to the MOSFET.

10. Revision History

Rev.	Date	Description
3.02	Apr 13, 2023	Updated the System Voltage Rail Short Protection section.
3.01	Dec 21, 2022	Updated Layout Guidelines for Pins 6 and 11.
3.00	Aug 24, 2021	Updated Figures 1, 2, and 3. Updated Ordering Information table format. Removed Way Overcurrent Protection information throughout the document.
2.00	May 13, 2021	Updated Figure 23. Updated the bullets under the SMBus Commands section on page 24. Updated the Control6 default value in Table 2. Updated the Battery Ship Mode section. Updated the System Overvoltage Protection section by changing 300mV to 400mV. Updated the System Voltage Rail Short Protection section. Added the System Voltage Undervoltage Protection (for Short-Circuit Protection) section.
1.01	Jul 23, 2020	Removed ISL9538CEVAL1Z from ordering information table. Updated the PSYS gain values in the PSYS pin description. Added PROCHOT# to the ACIN Parameter name in Abs Max section. Updated test condition for the Entering Ideal Diode Mode VSYS Voltage Threshold specification on page 13. Added Note 9 and the cross-reference to the Control6 Register 0x37H table. Updated the VSYS Layout Guideline description on page 57.
1.00	Oct 10, 2019	Initial release

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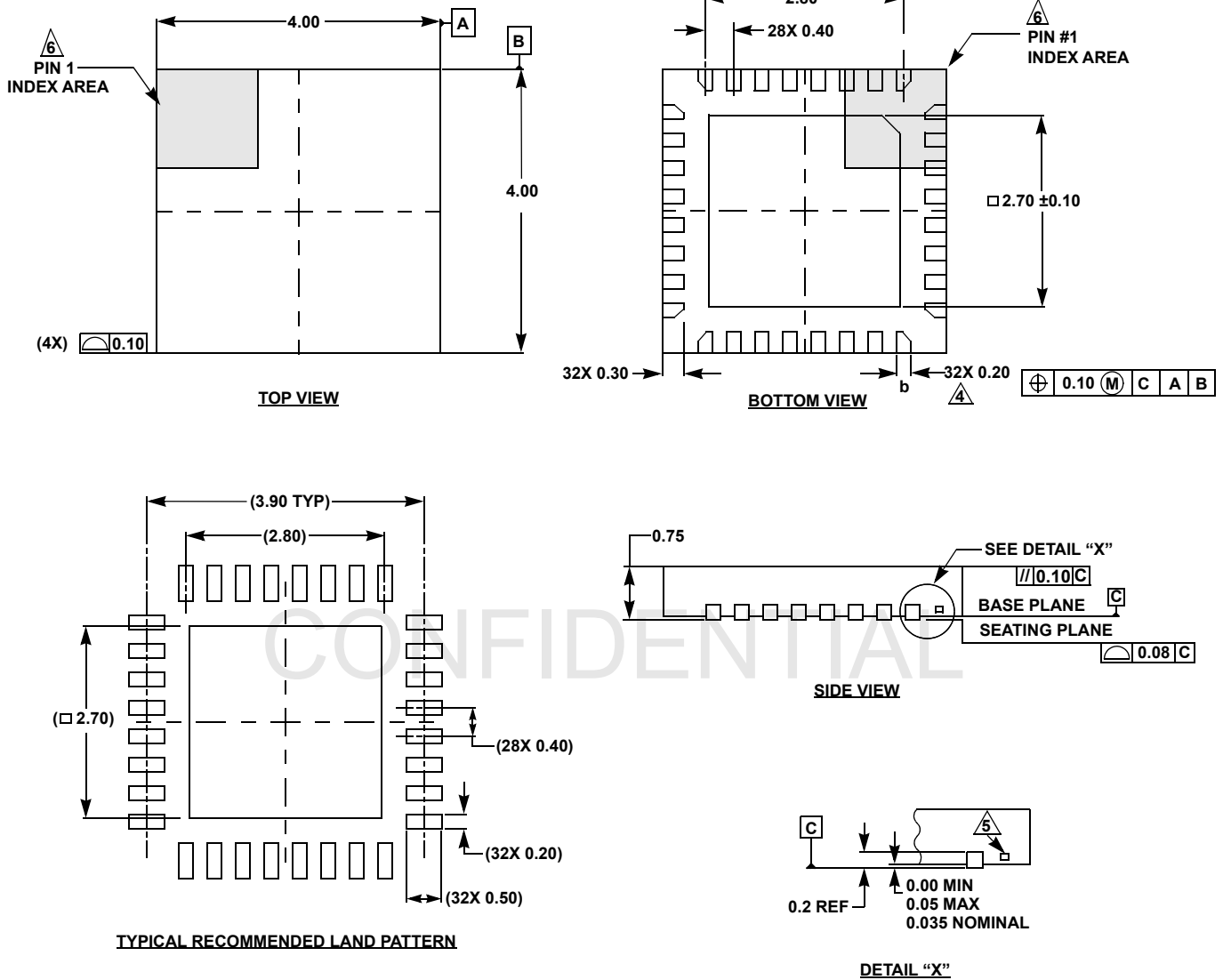
11. Package Outline Drawing

For the most recent package outline drawing, see [L32.4x4D](#).

L32.4x4D

32 Lead Thin Quad Flat No-Lead Plastic Package

Rev 2, 10/16



NOTES:

1. Dimensions are in millimeters.
Dimensions in () for Reference Only.
2. Dimensioning and tolerancing conform to ASME Y14.5m-1994.
3. Unless otherwise specified, tolerance: Decimal ± 0.05 .
4. Dimension b applies to the metallized terminal and is measured between 0.15mm and 0.25mm from the terminal tip.
5. Tiebar shown (if present) is a non-functional feature.
6. The configuration of the pin #1 identifier is optional, but must be located within the zone indicated. The pin #1 identifier may be either a mold or mark feature.

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